

Characterization of SiPMs

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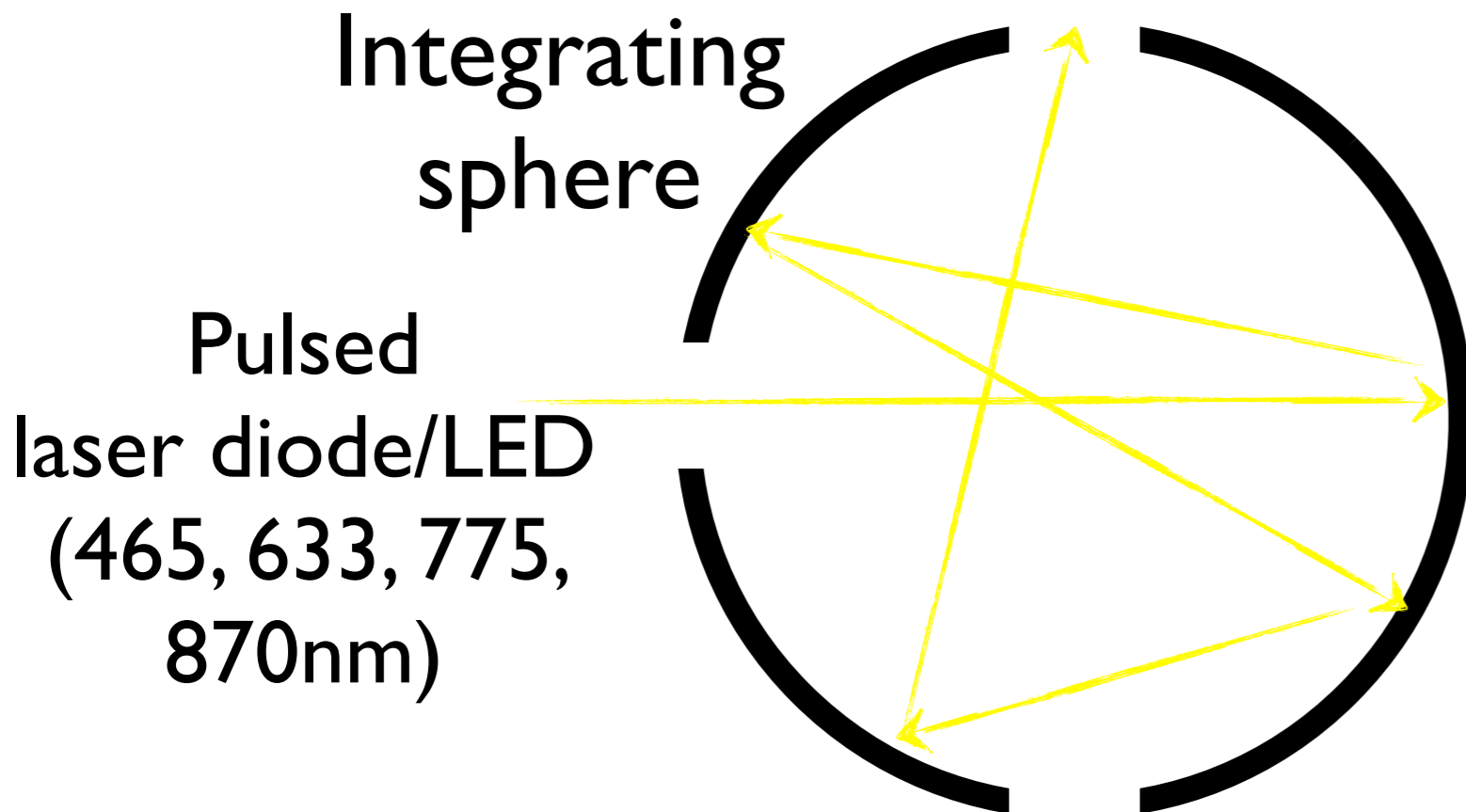
Overview

- Complete test setup for SiPM measurements has been established
 - Dark-rate (T)
 - Cross-talk probability (T)
 - After-pulse probability (T)
 - PDE measurement
 - Uniformity scans
 - Photon counting resolution

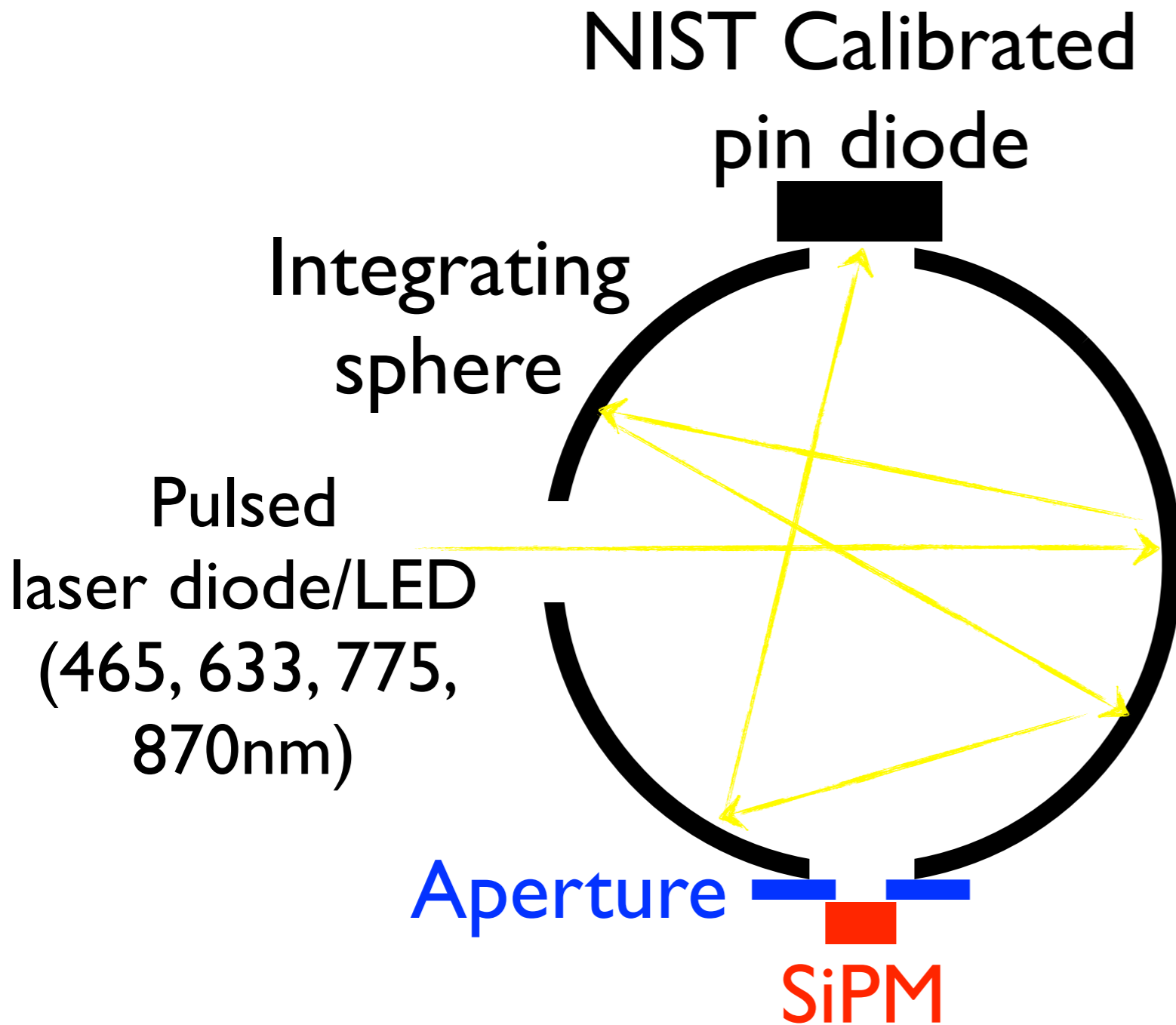
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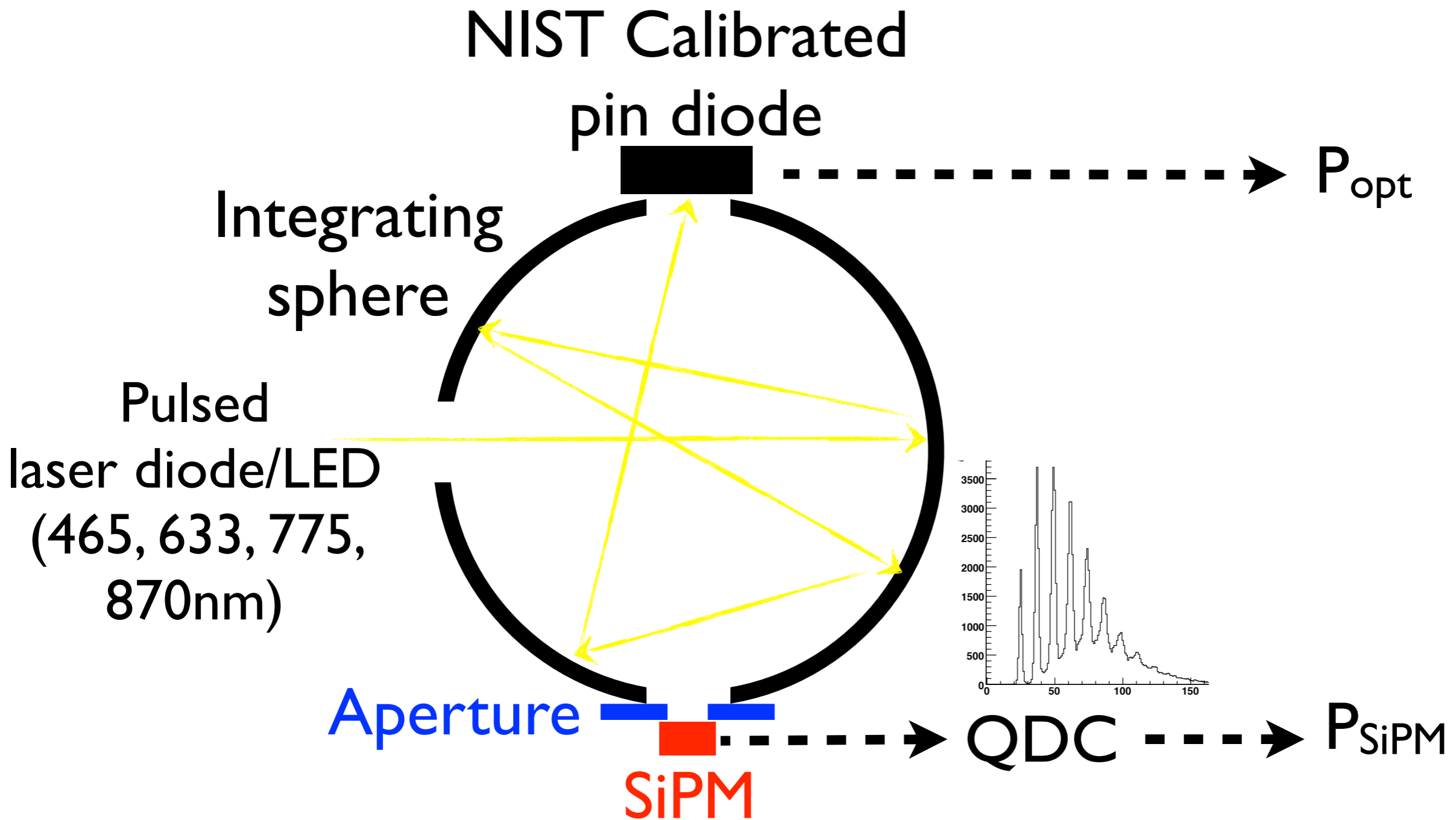
Setup: Absolute PDE



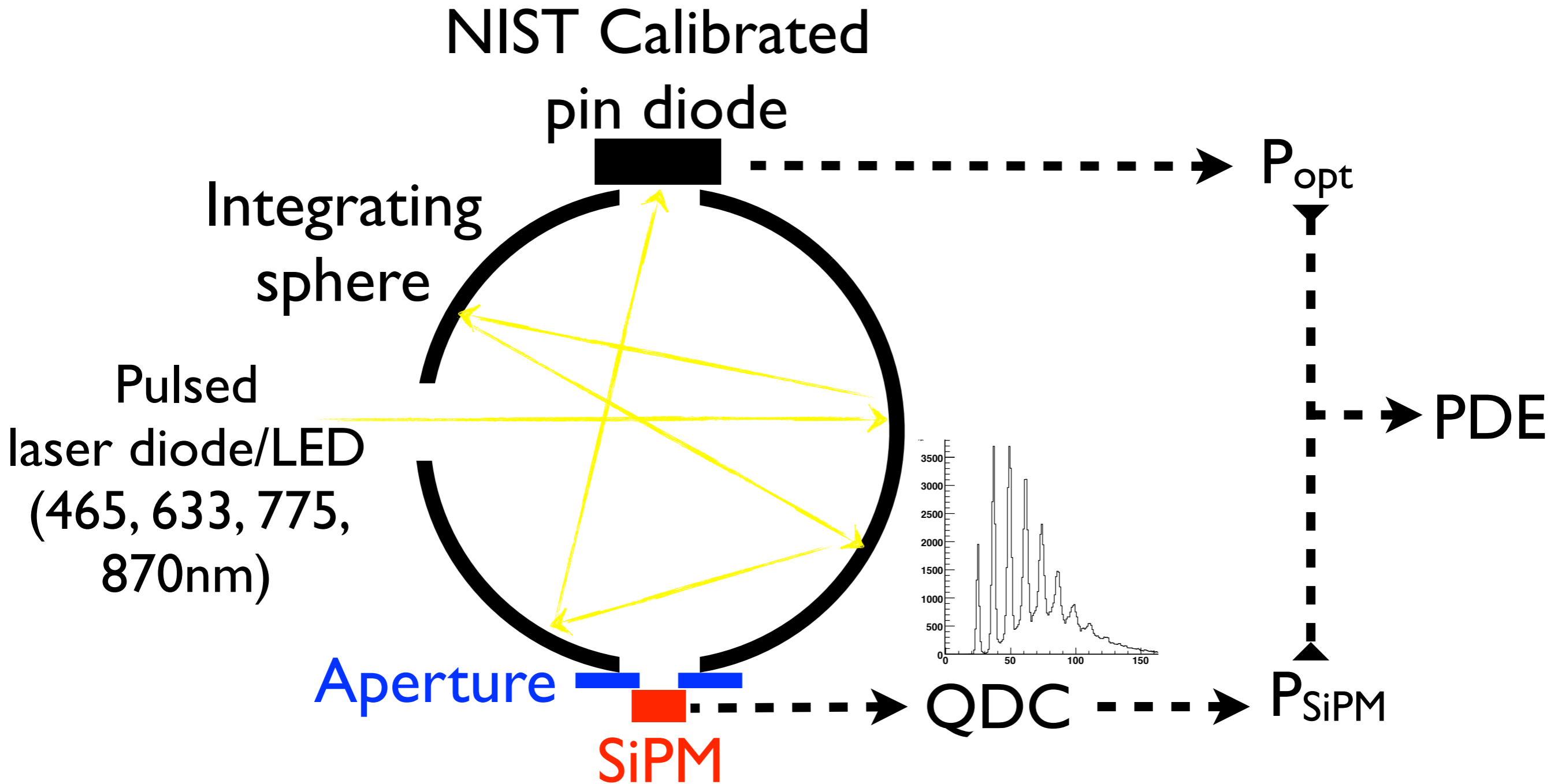
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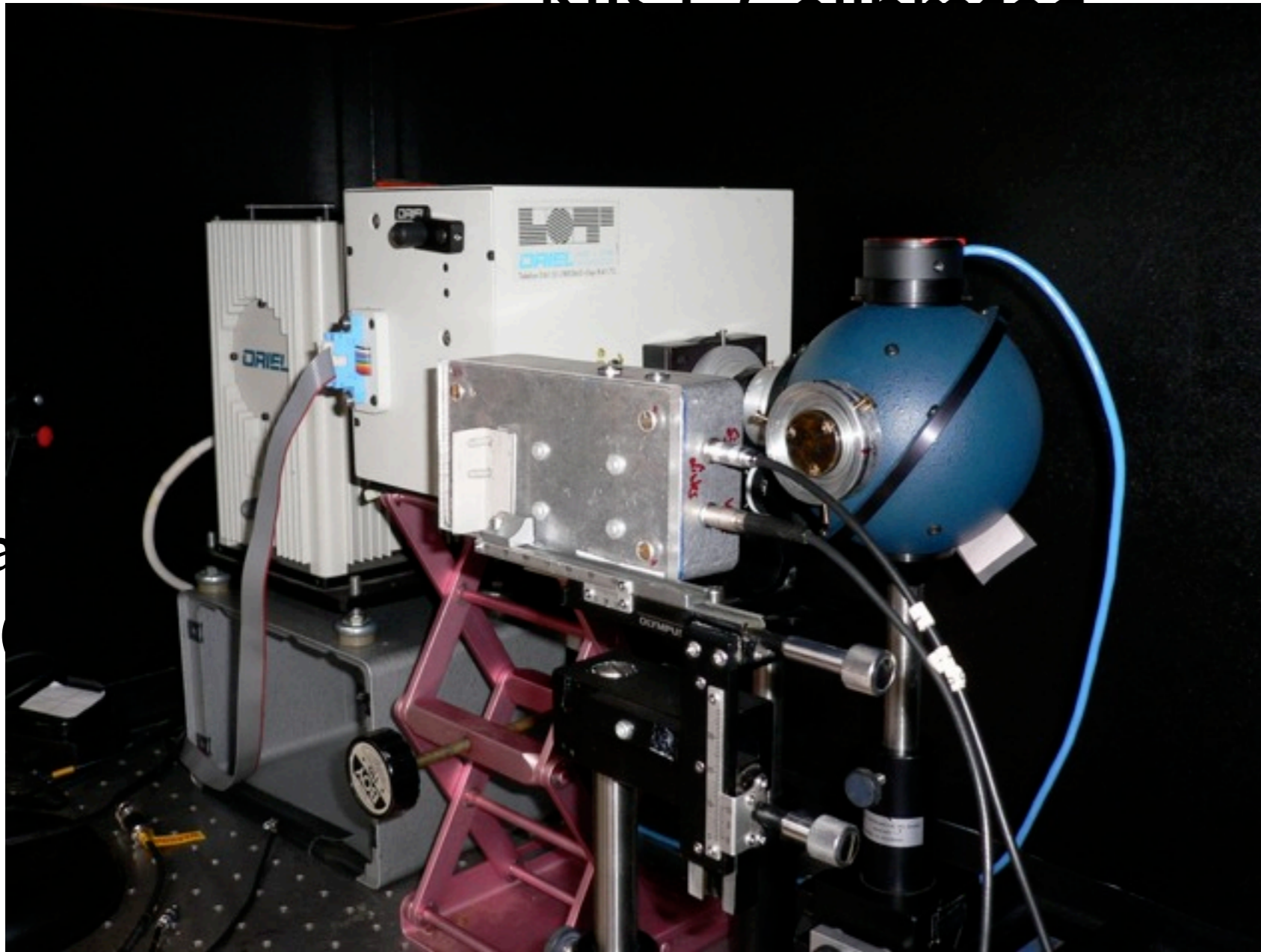


Setup: Absolute PDE

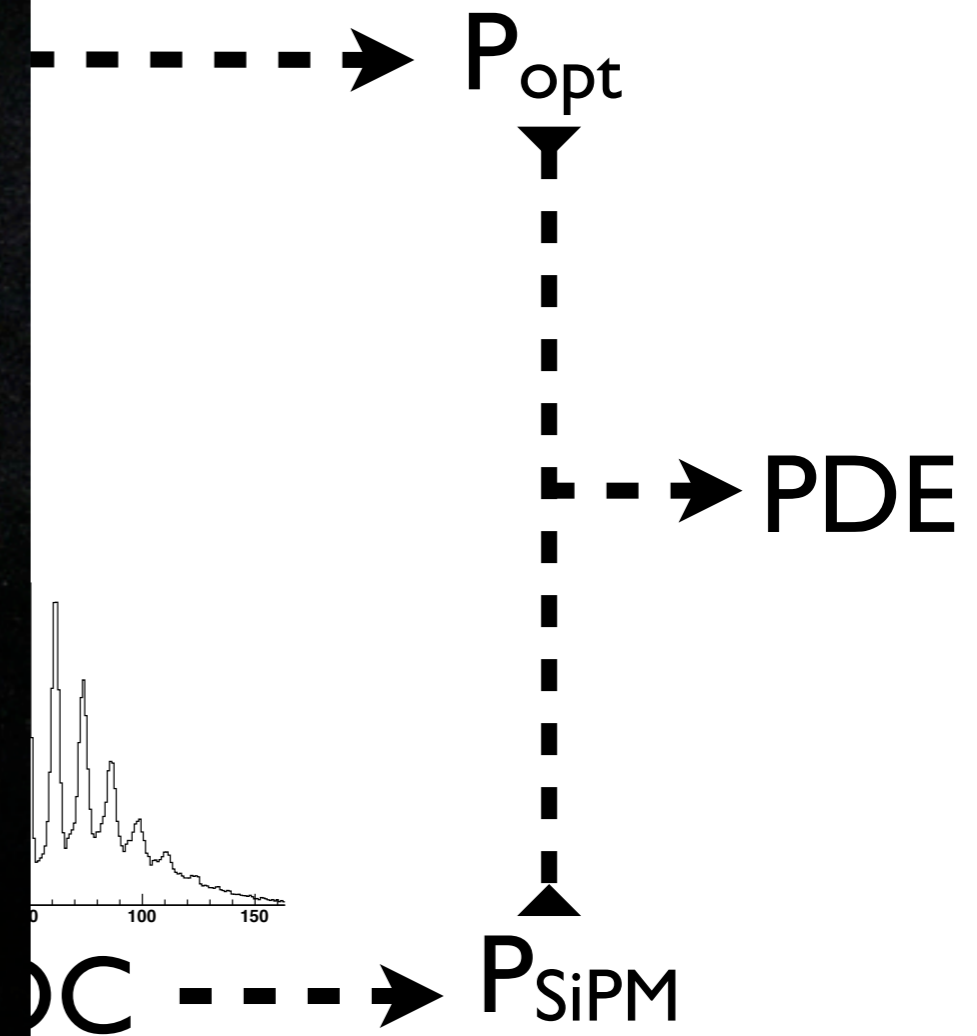


Setup: Absolute PDE

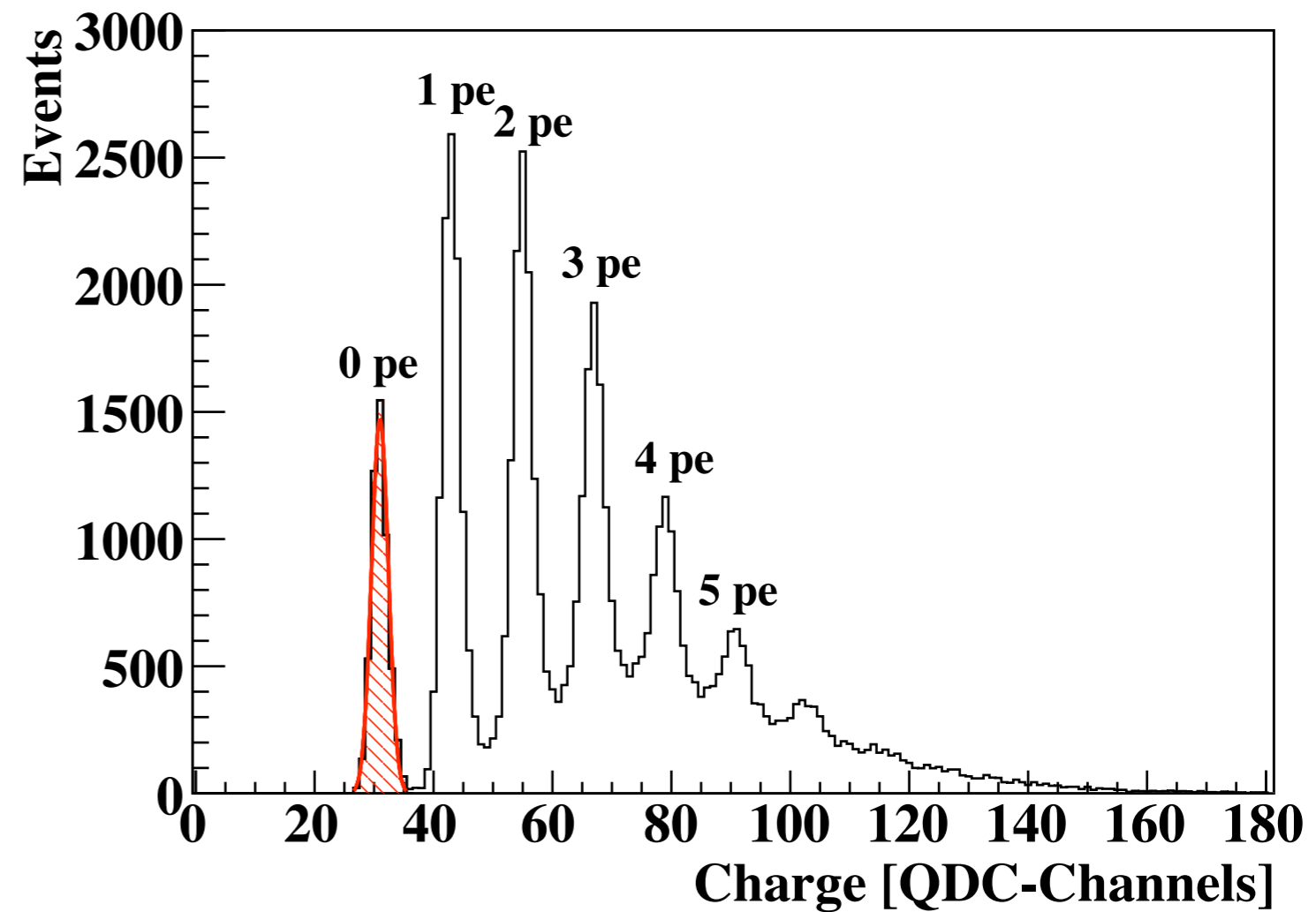
NIST Calibrated



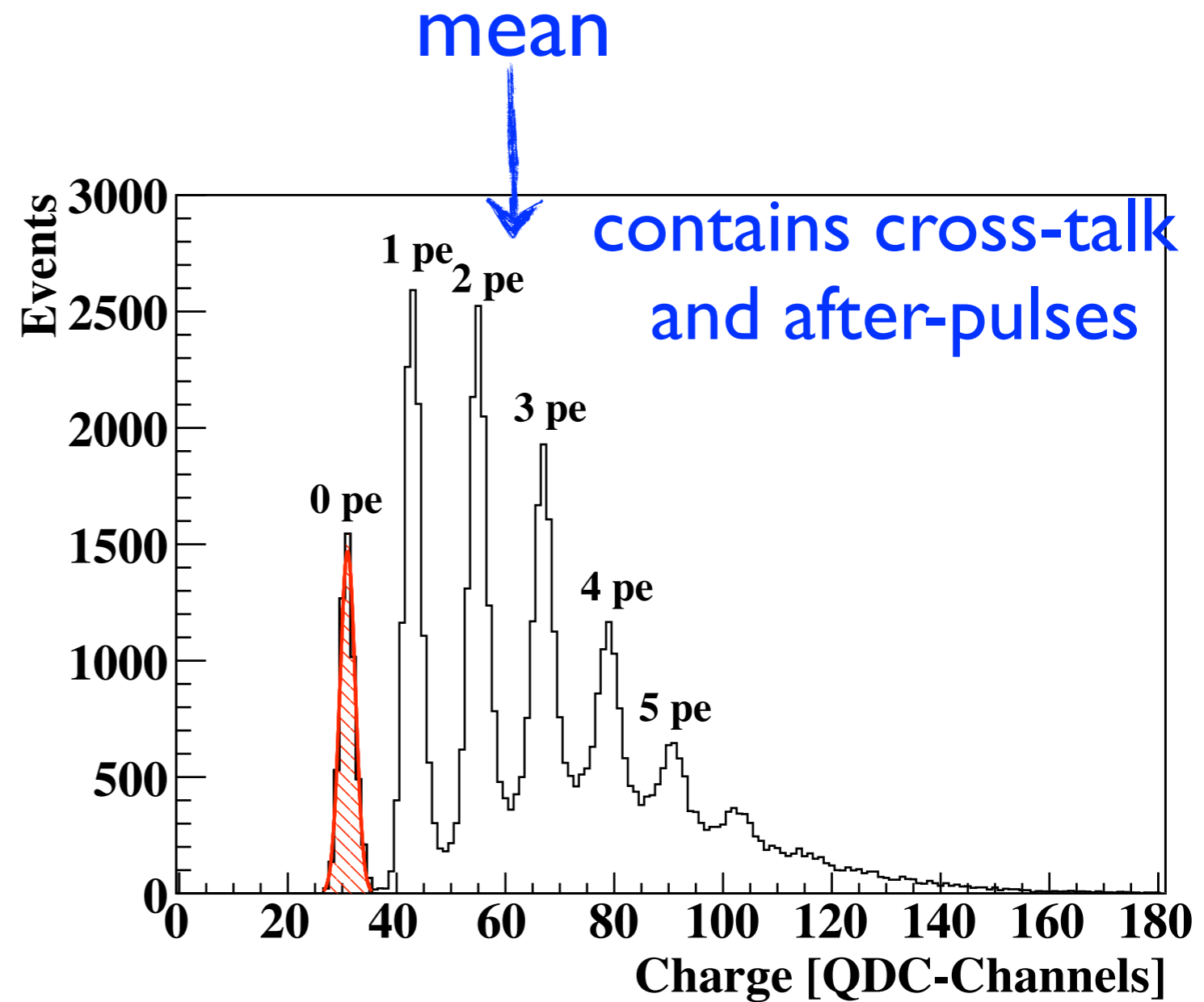
SIPM



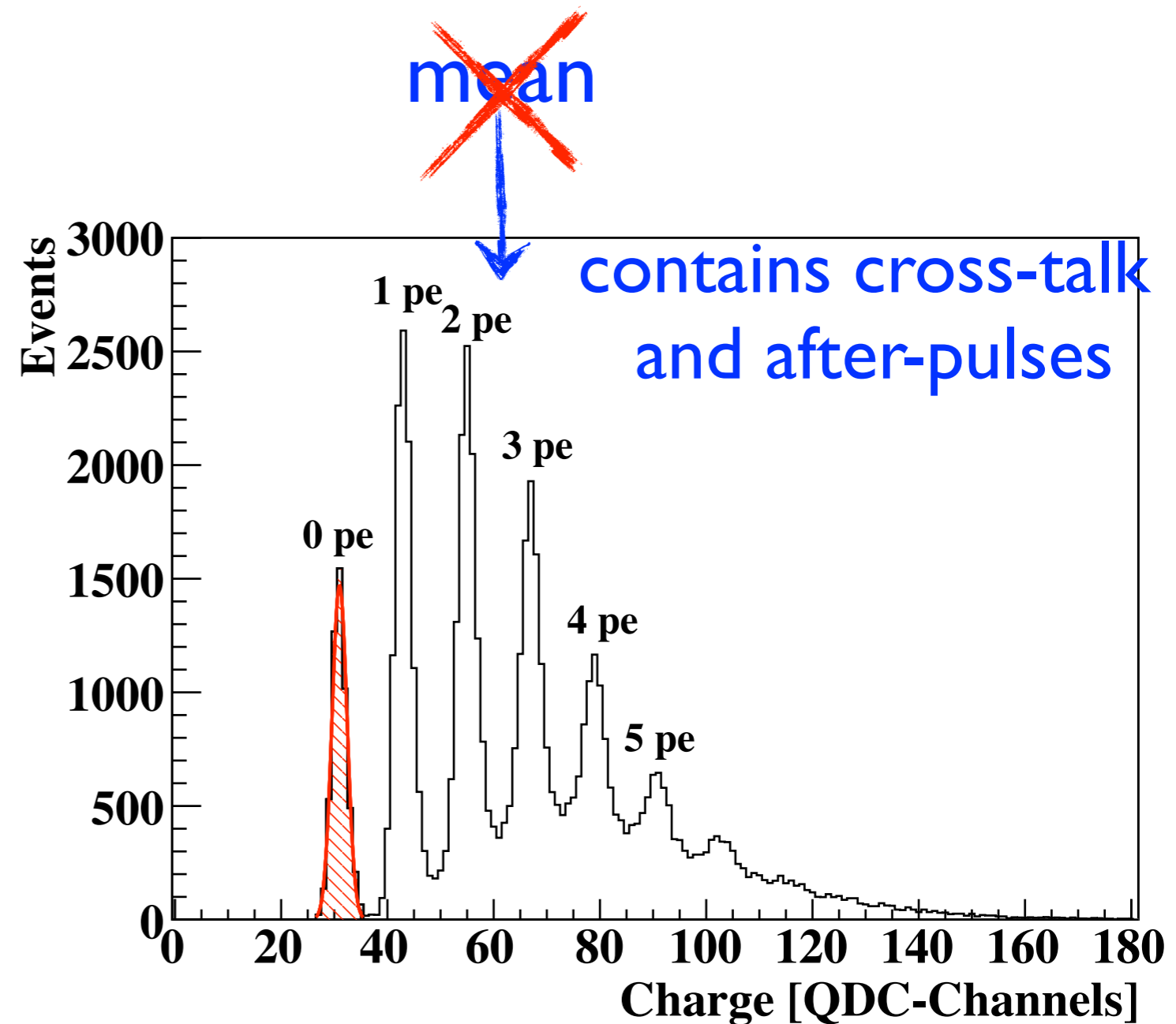
Statistical Analysis



Statistical Analysis



Statistical Analysis

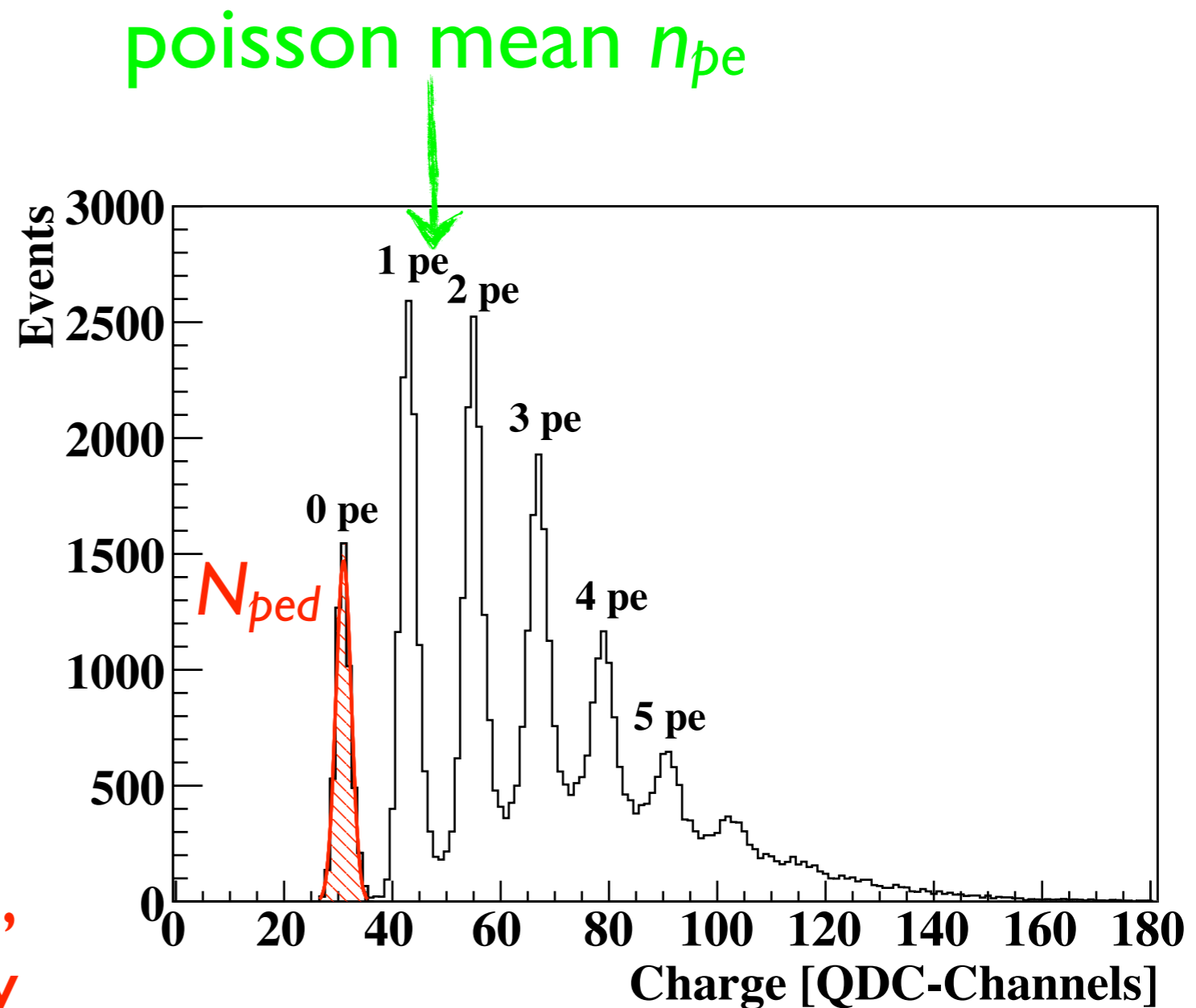


Statistical Analysis

Poisson:

$$\begin{aligned} P(0, n_{pe}) &= e^{-n_{pe}} \\ \rightarrow n_{pe} &= -\ln(P(0, n_{pe})) \\ &= -\ln\left(\frac{N_{ped}}{N_{tot}}\right) + \ln\left(\frac{N_{ped}^{dark}}{N_{tot}^{dark}}\right) \end{aligned}$$

Number of pedestal events, N_{ped} , not influenced by cross-talk and after-pulses



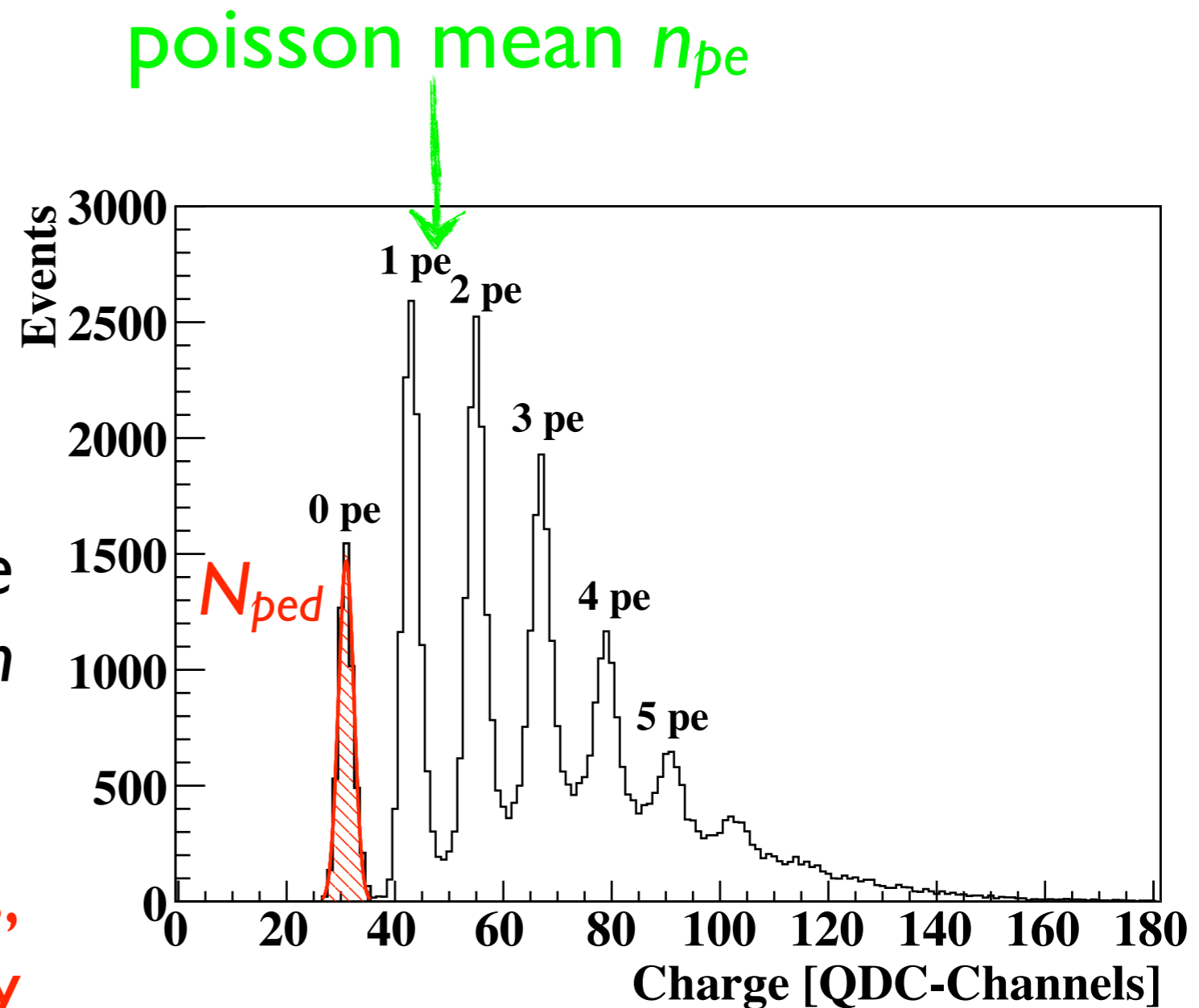
Statistical Analysis

Poisson:

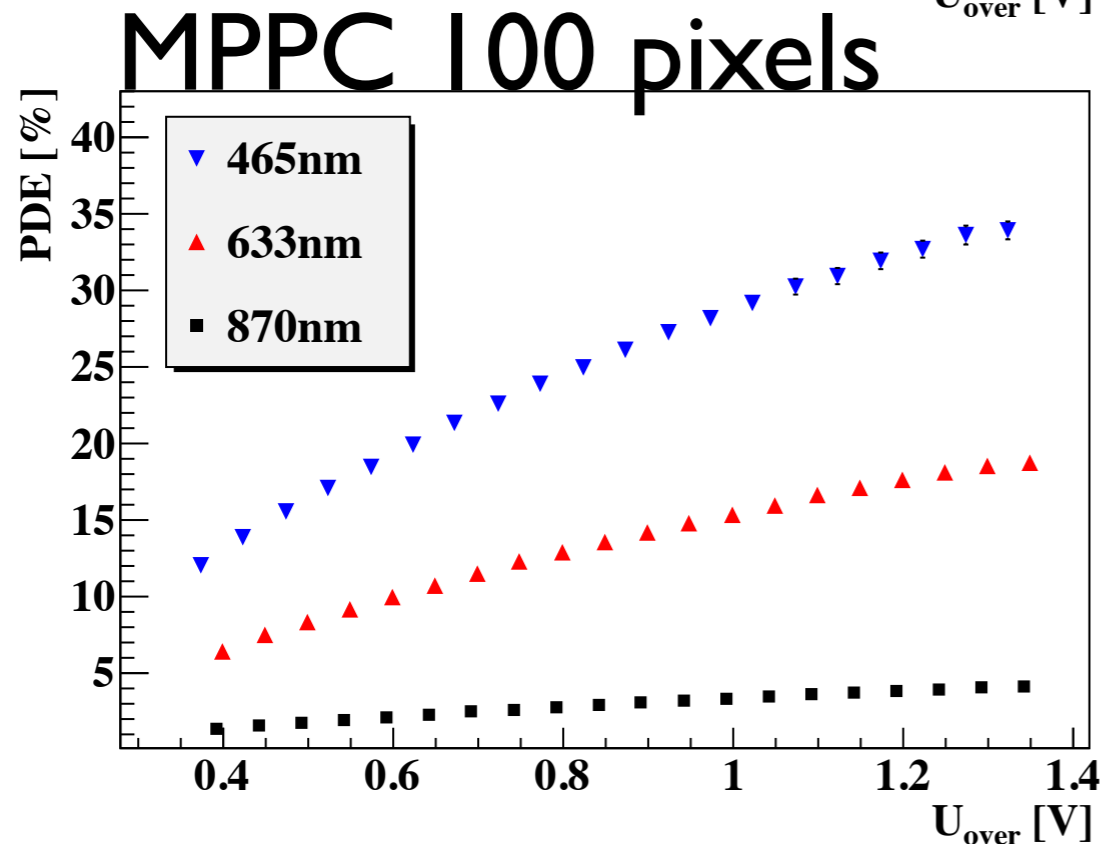
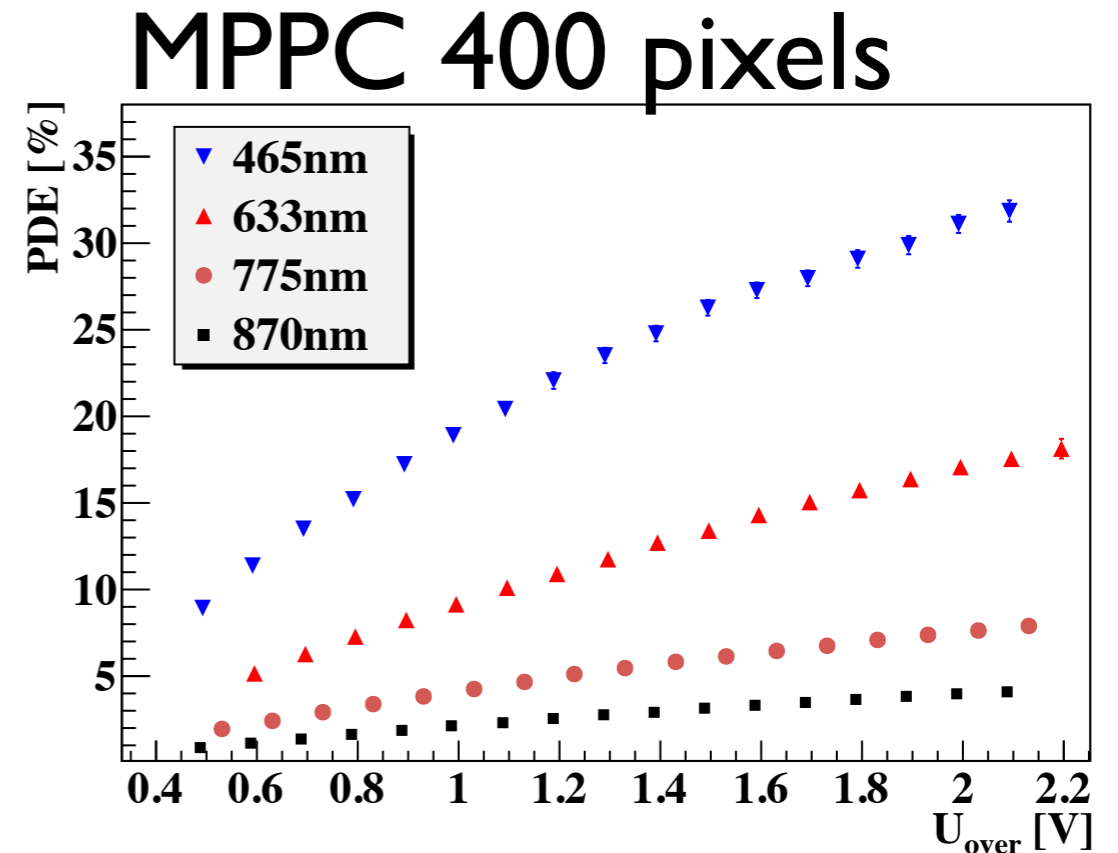
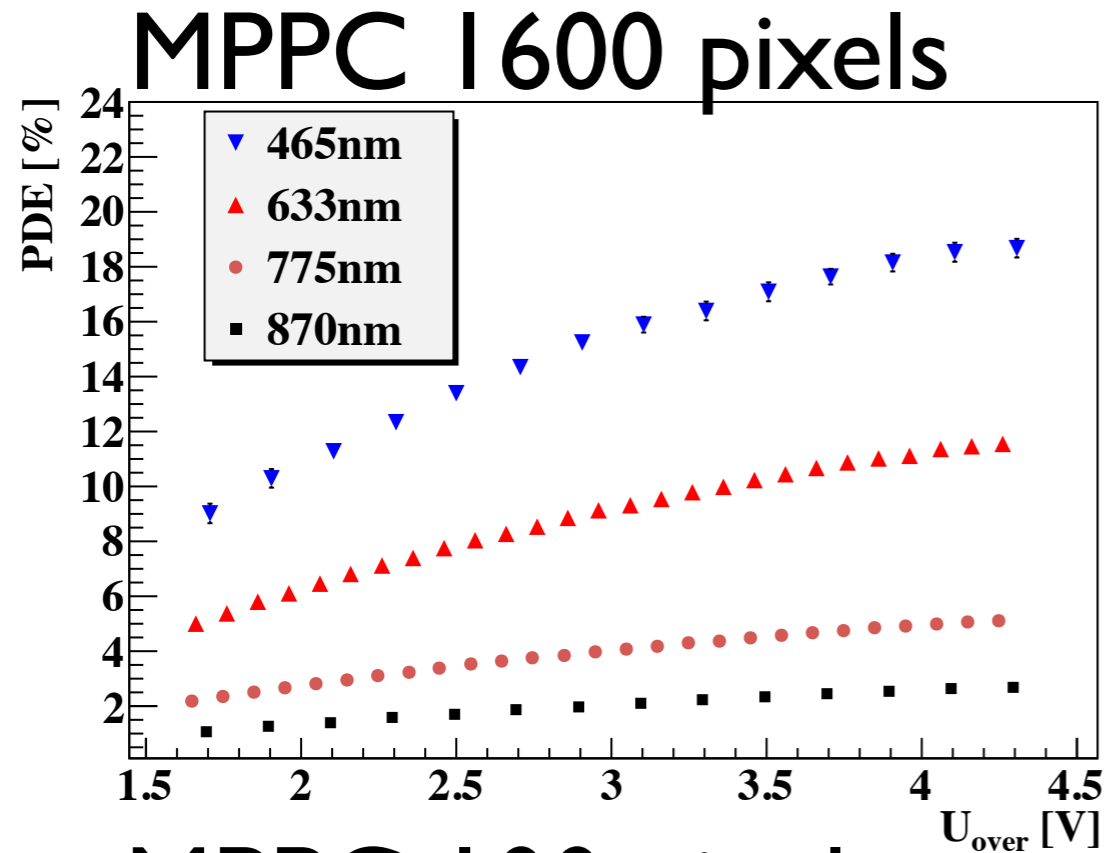
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Dark-rate
correction
(small)

Number of pedestal events,
 N_{ped} , not influenced by
cross-talk and after-pulses



PDE vs. U_{over}

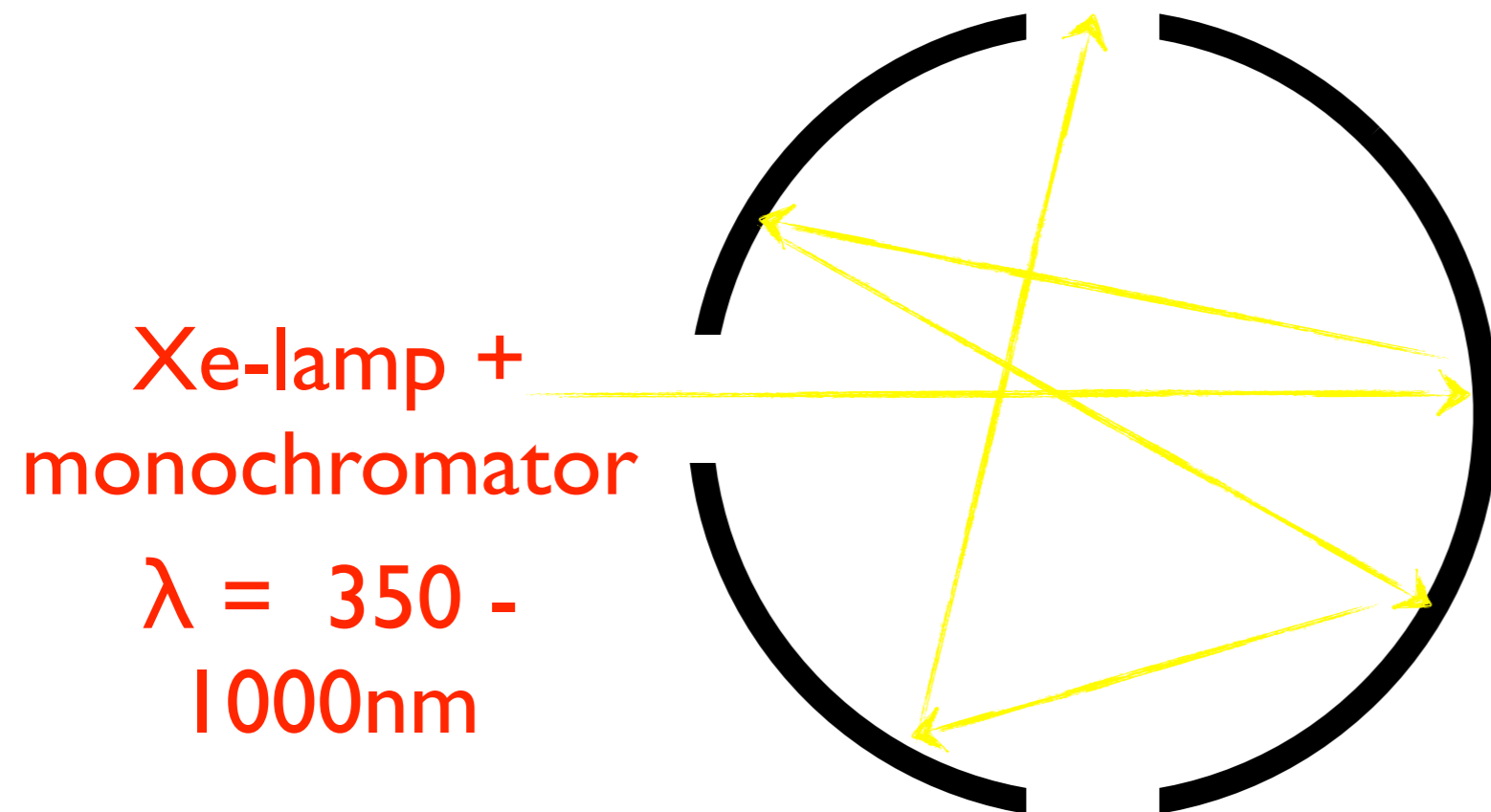


$$\begin{aligned}
 PDE &= \frac{P_{SiPM}}{P_{opt}} \\
 &= \frac{n_{pe} \cdot h\nu \cdot R \cdot f}{P_{opt}}
 \end{aligned}$$

R : Power ratio

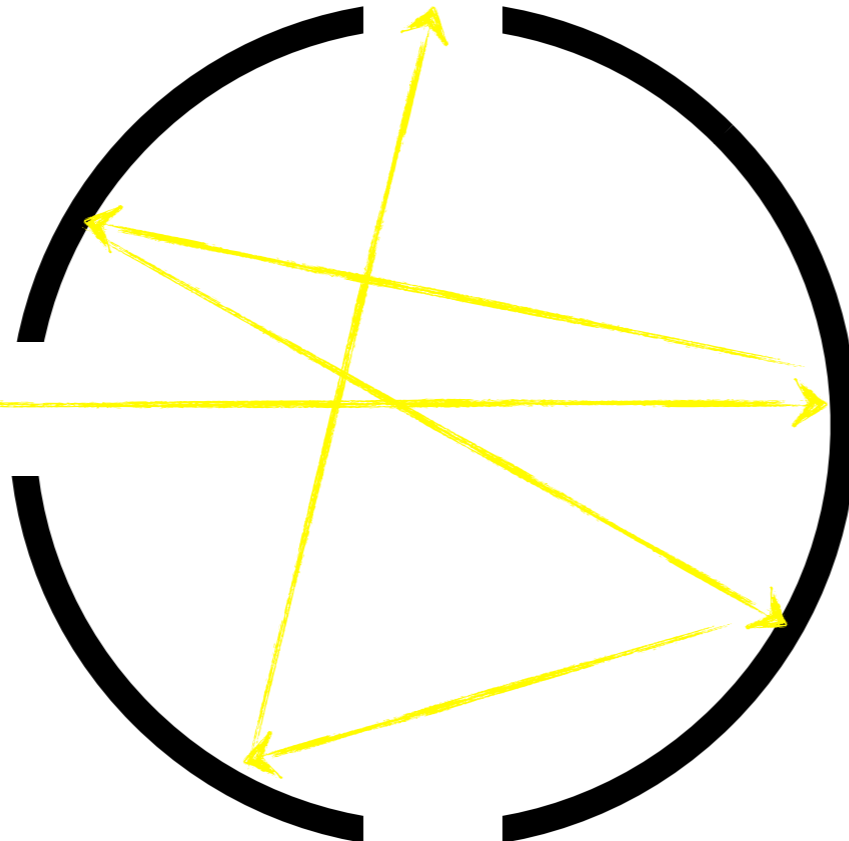
f : Pulsing frequency

Setup: Spectral Sensitivity



Setup: Spectral Sensitivity

NIST Calibrated
pin diode

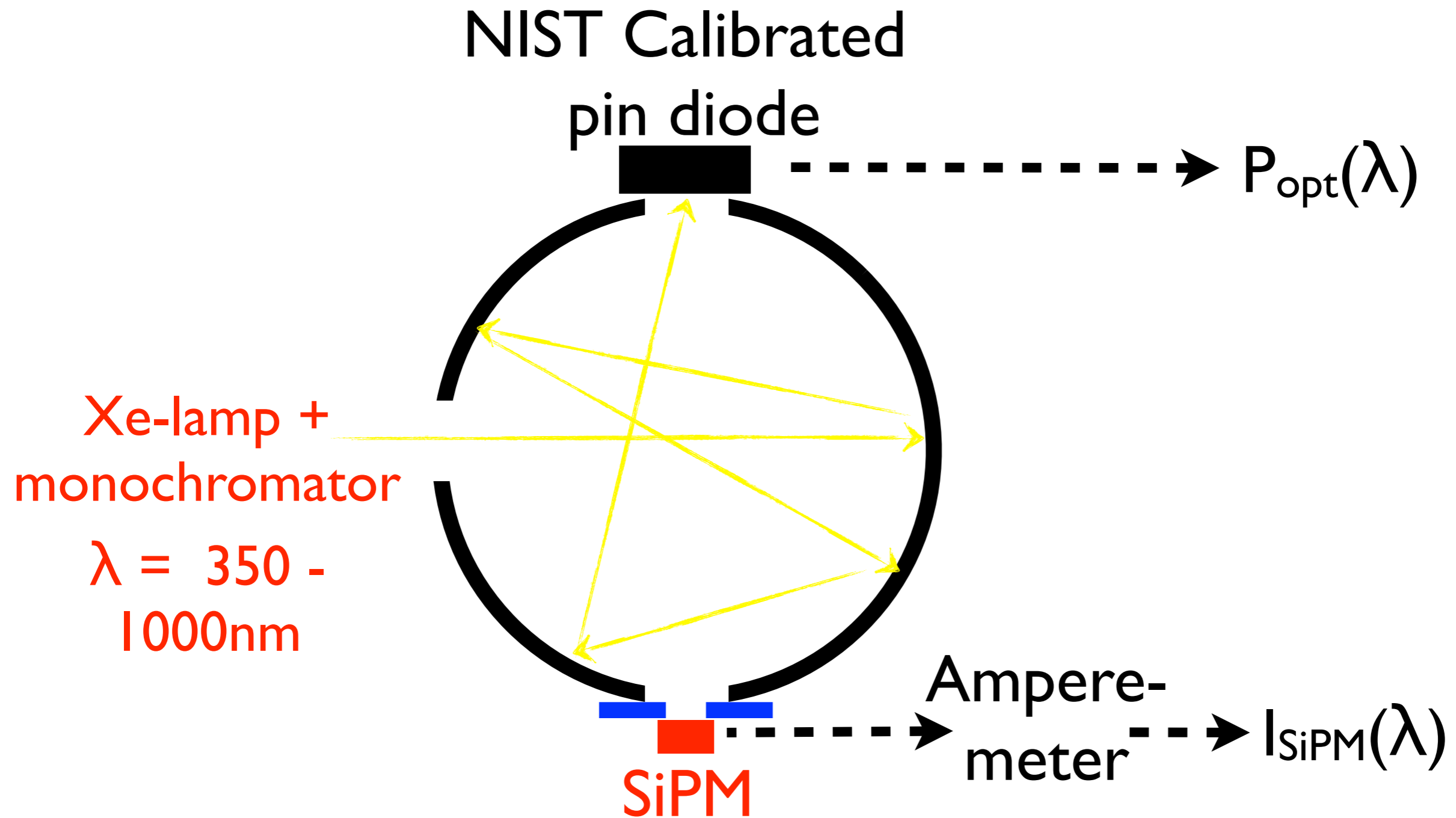


Xe-lamp +
monochromator

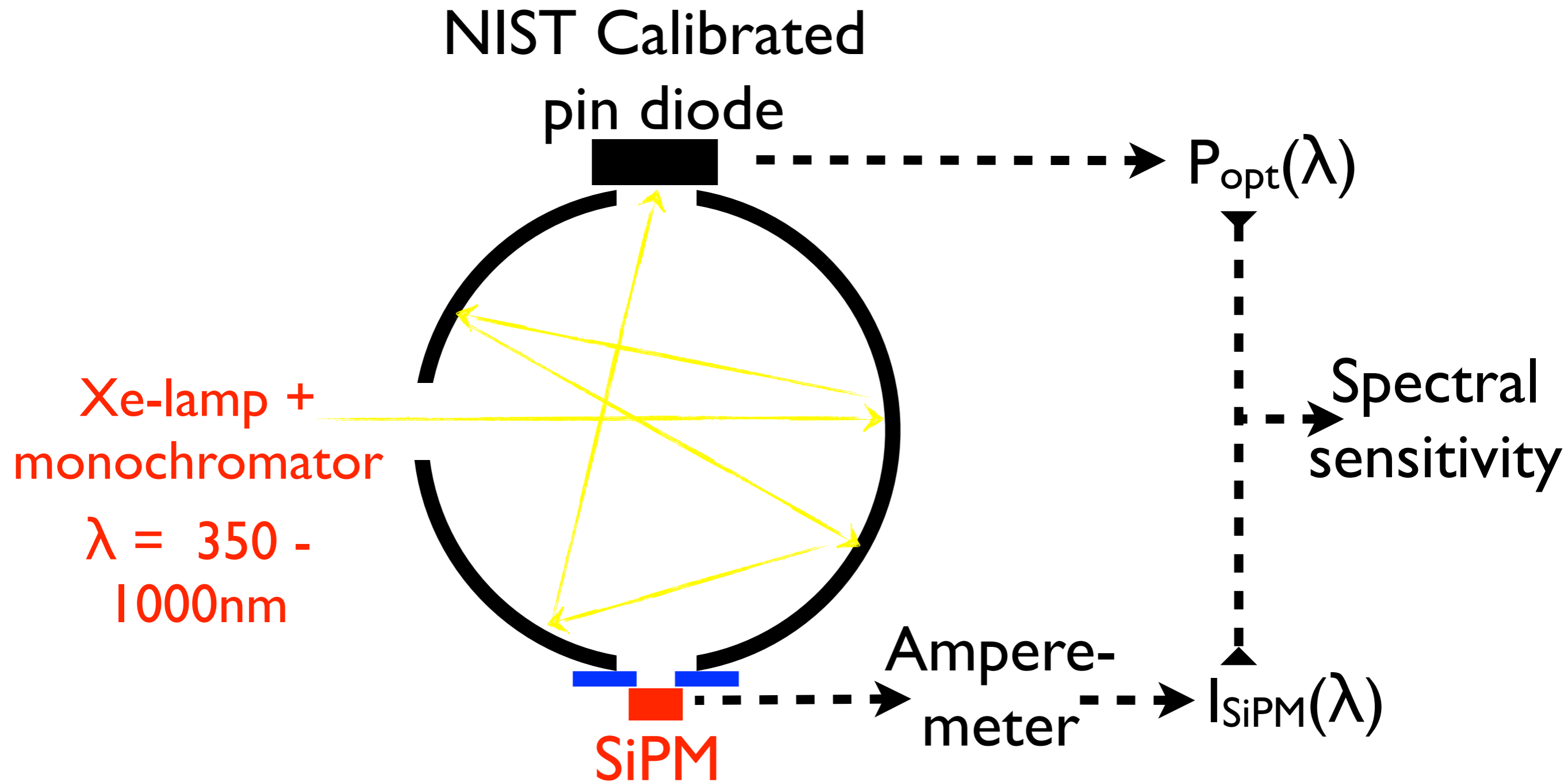
$\lambda = 350 -$
1000nm

SiPM

Setup: Spectral Sensitivity

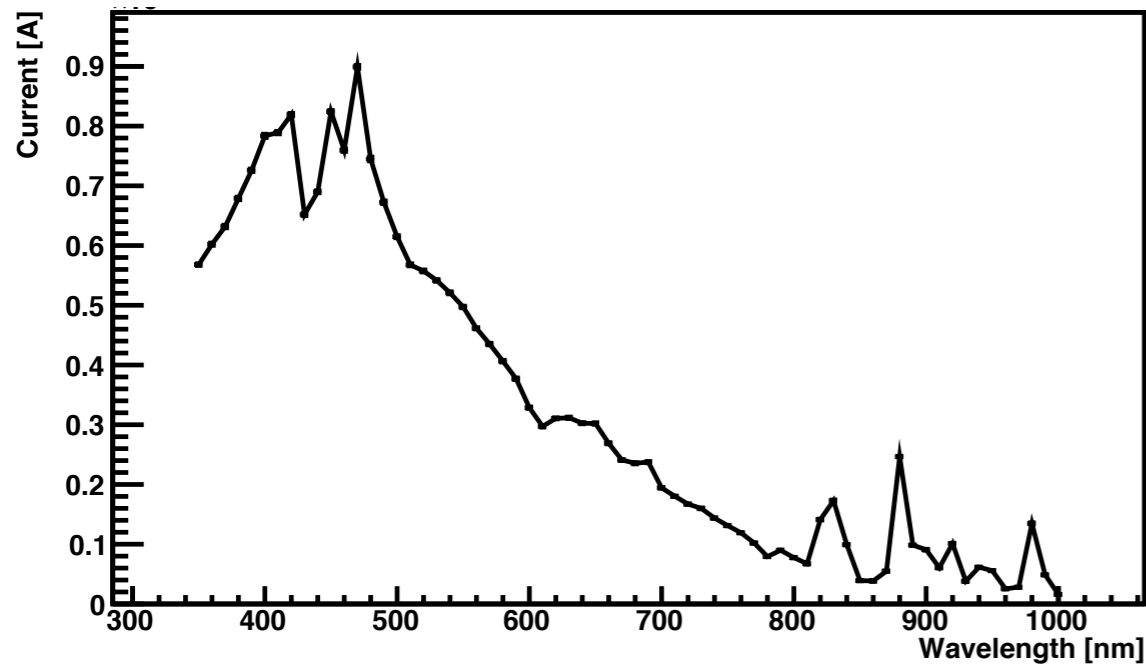


Setup: Spectral Sensitivity

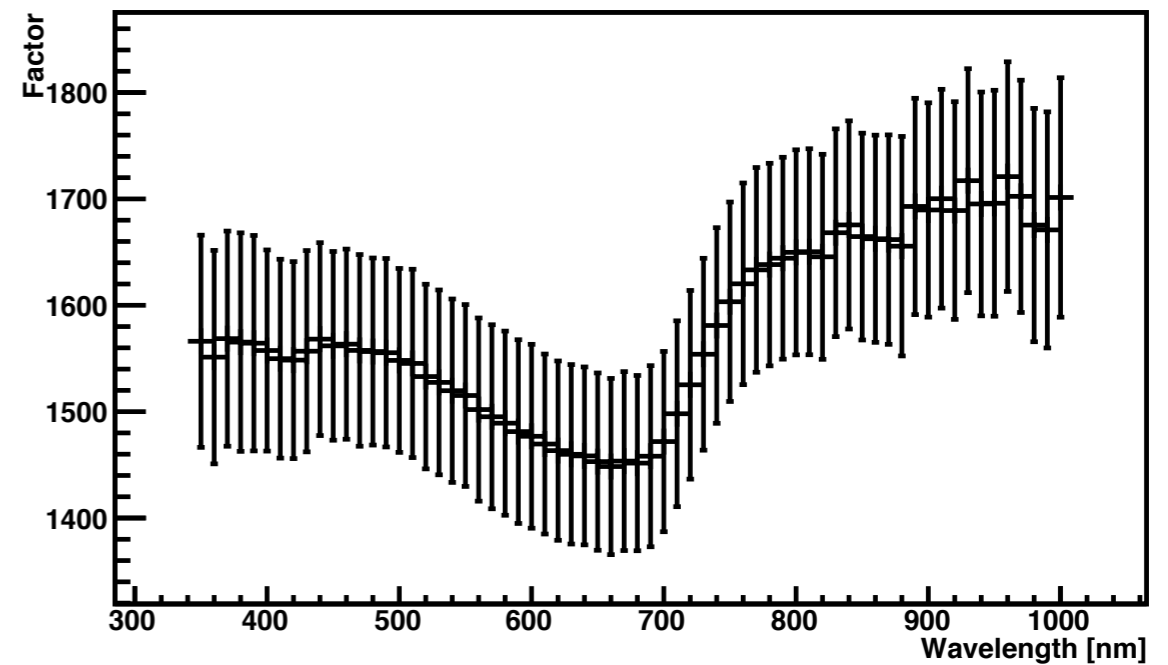


Spectral Sensitivity

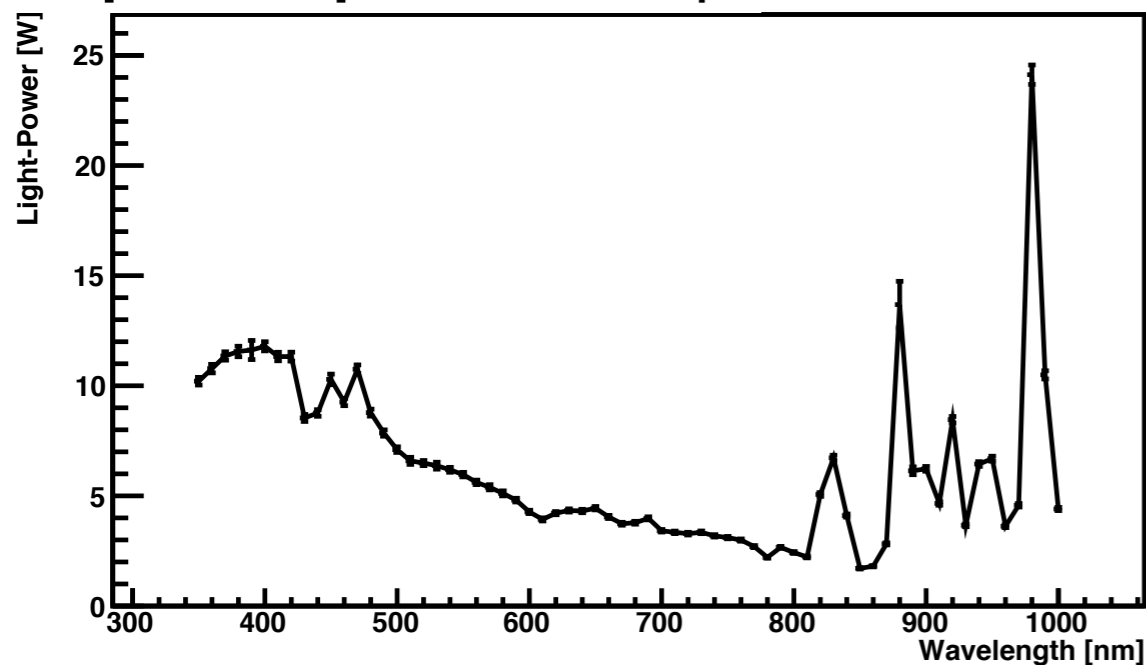
SiPM current, I_{SiPM} **A**



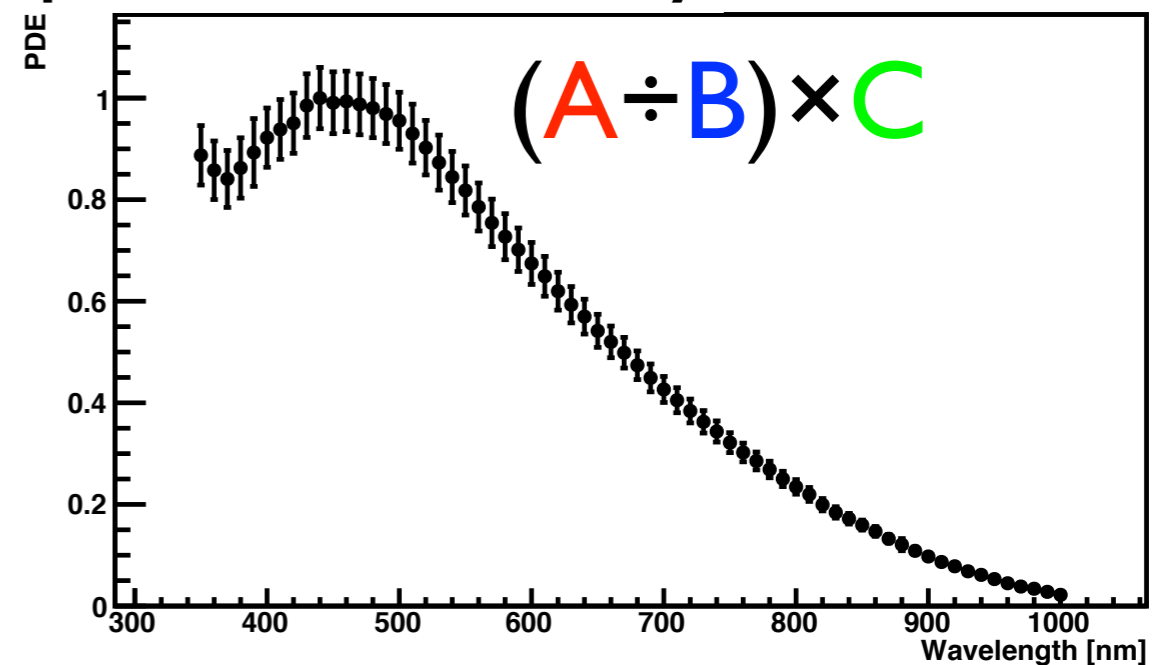
Power ratio **C**



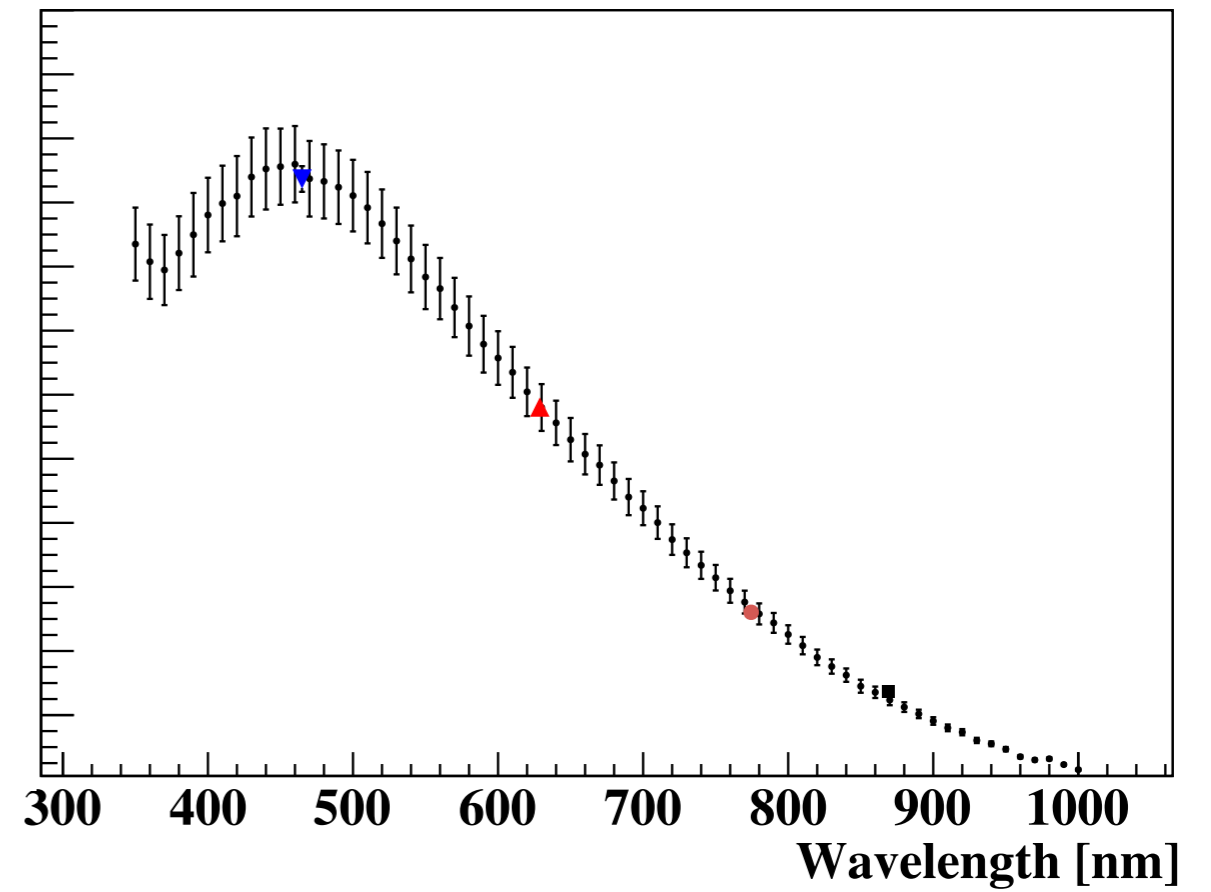
Optical power, P_{opt} **B**



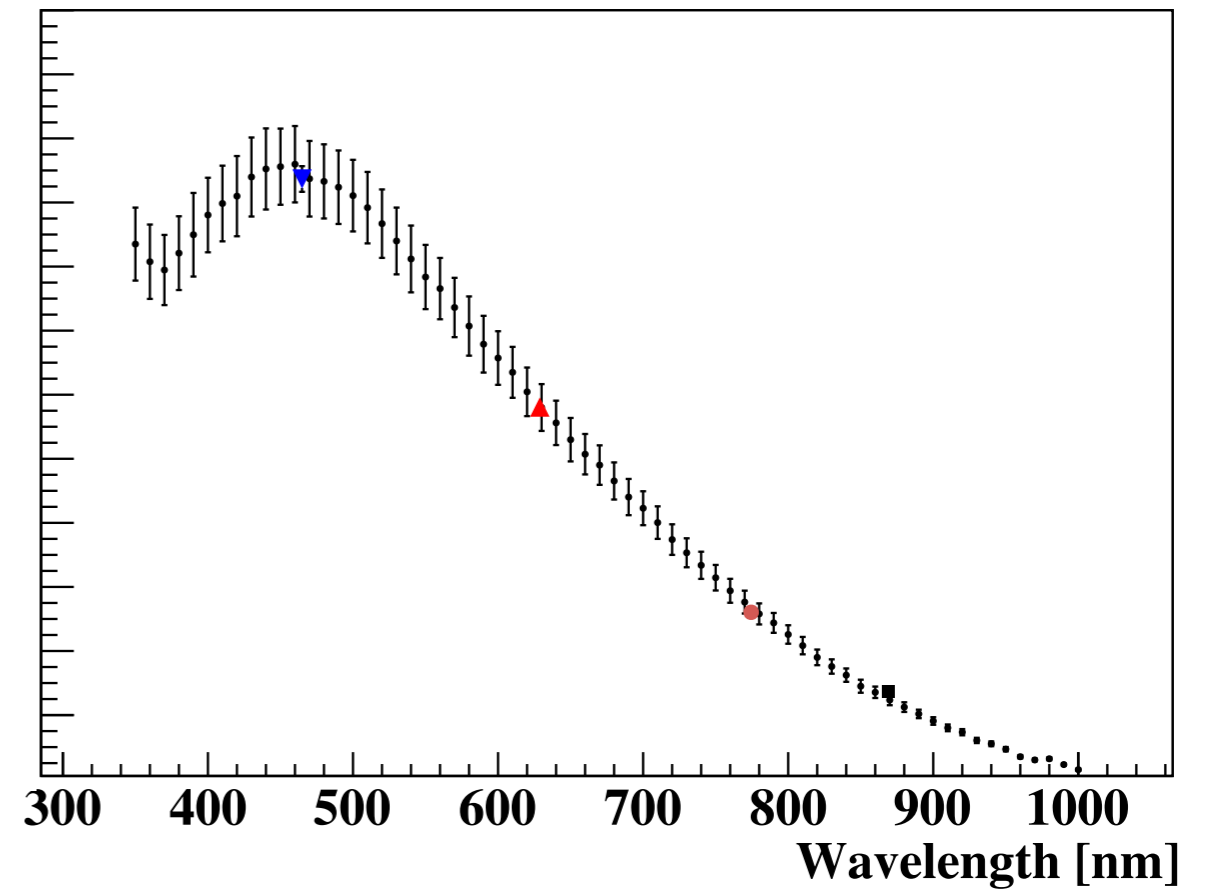
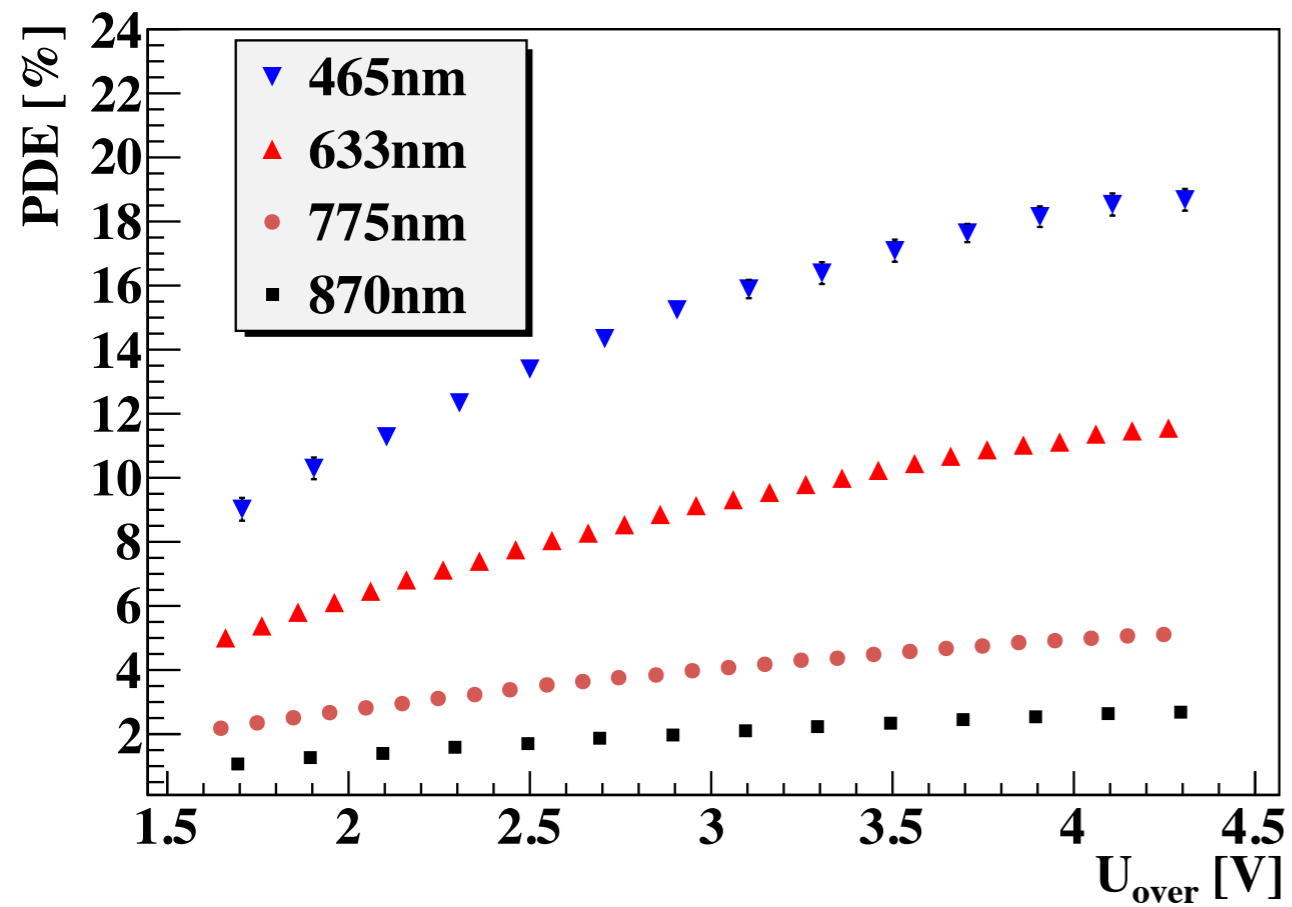
Spectral sensitivity



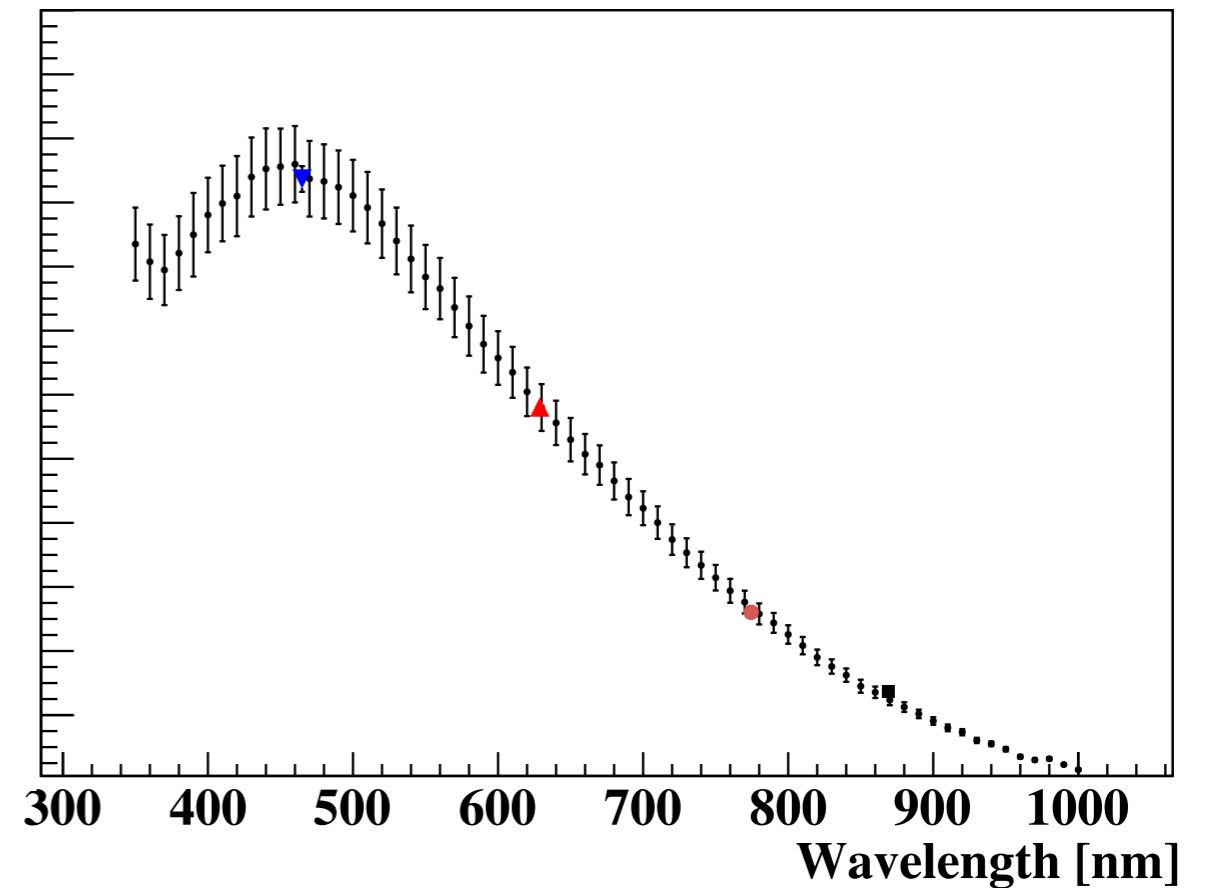
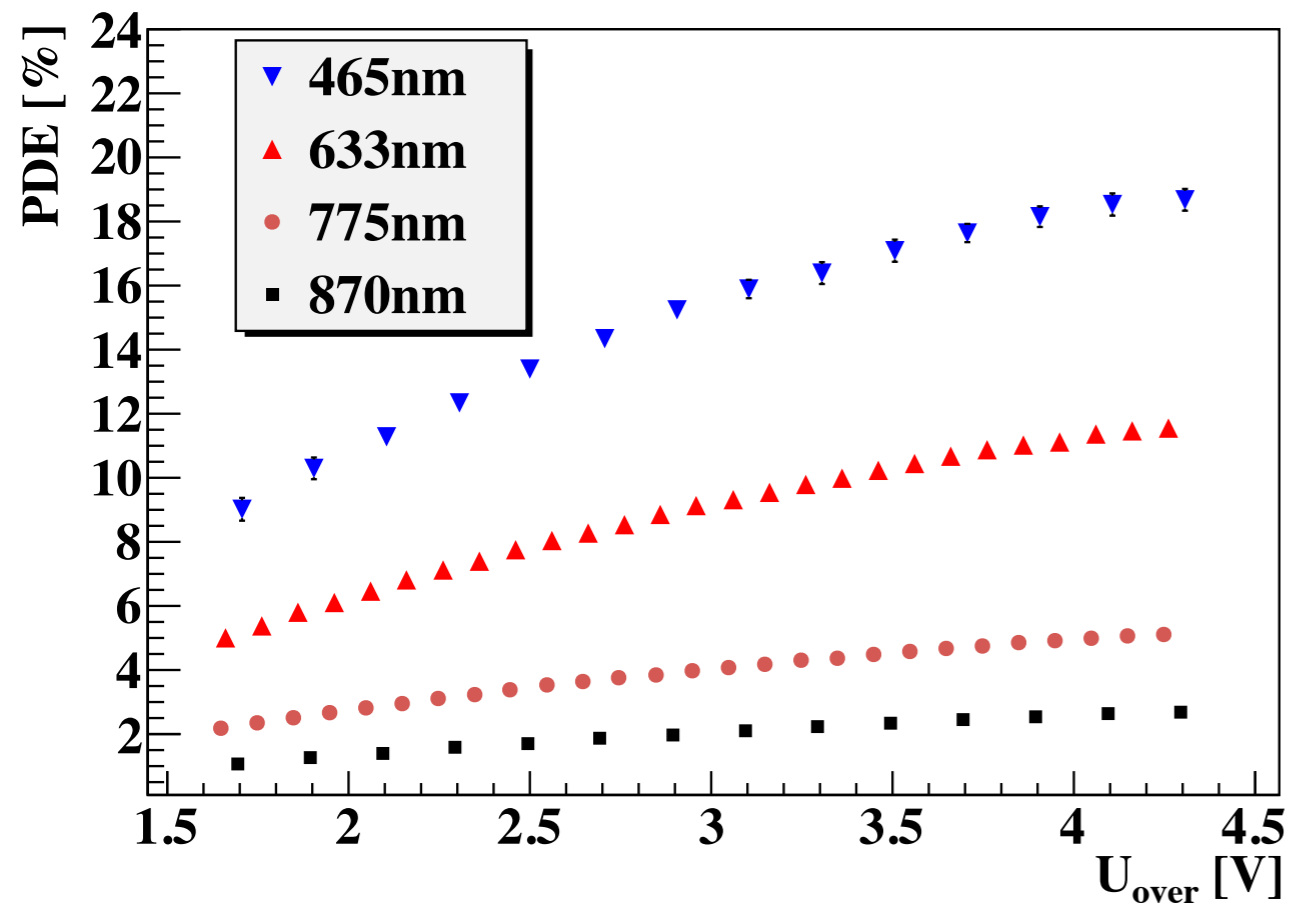
PDE Scaling



PDE Scaling

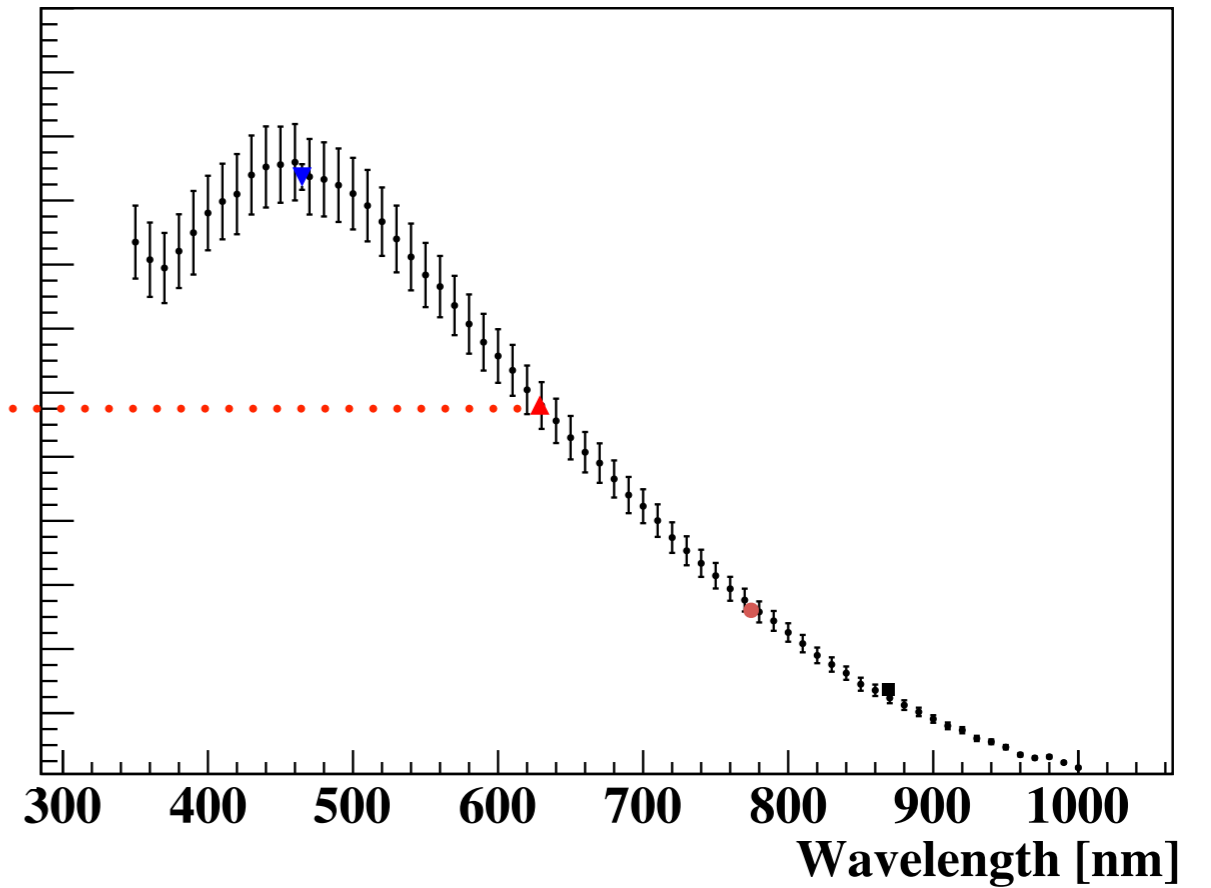
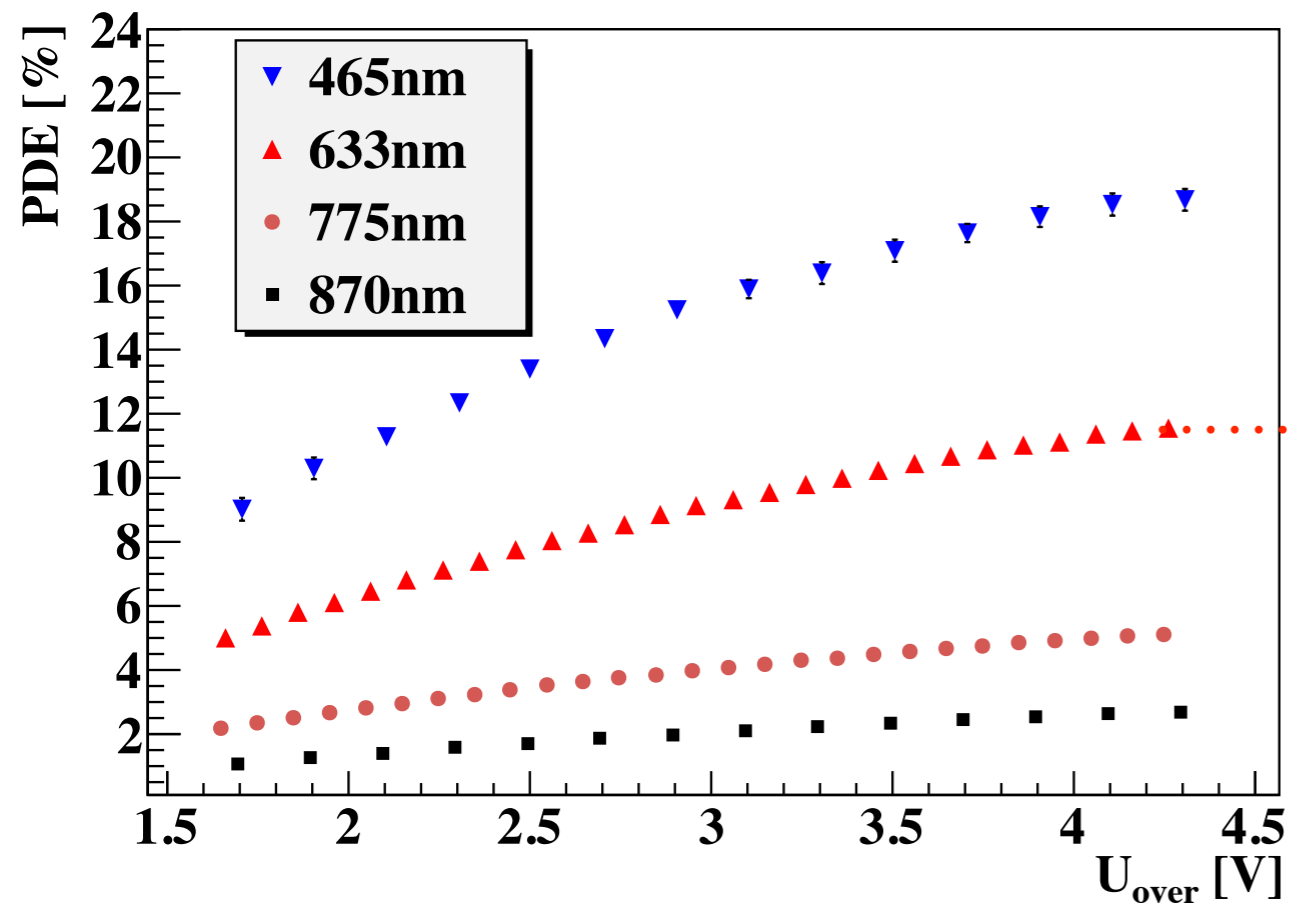


PDE Scaling



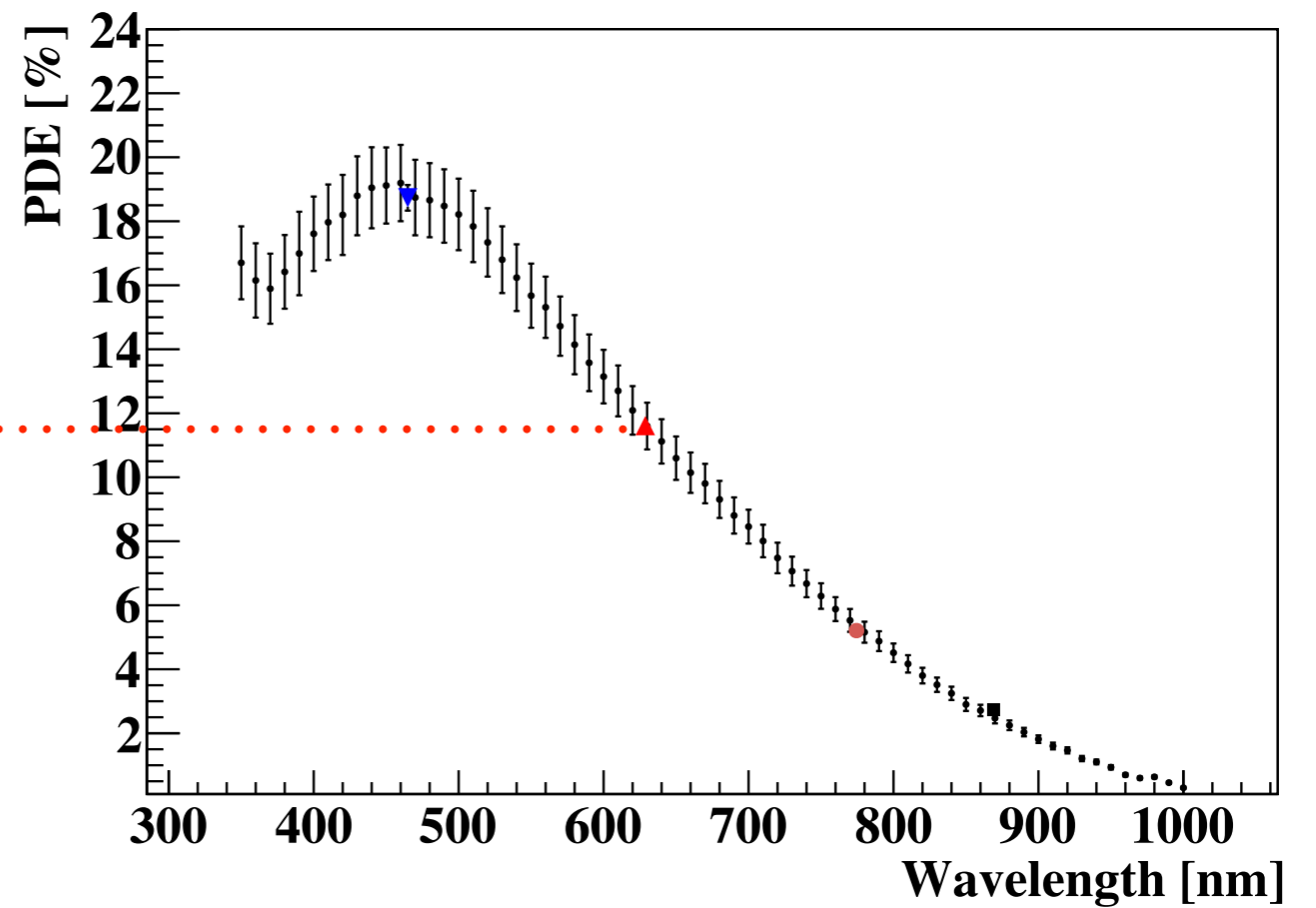
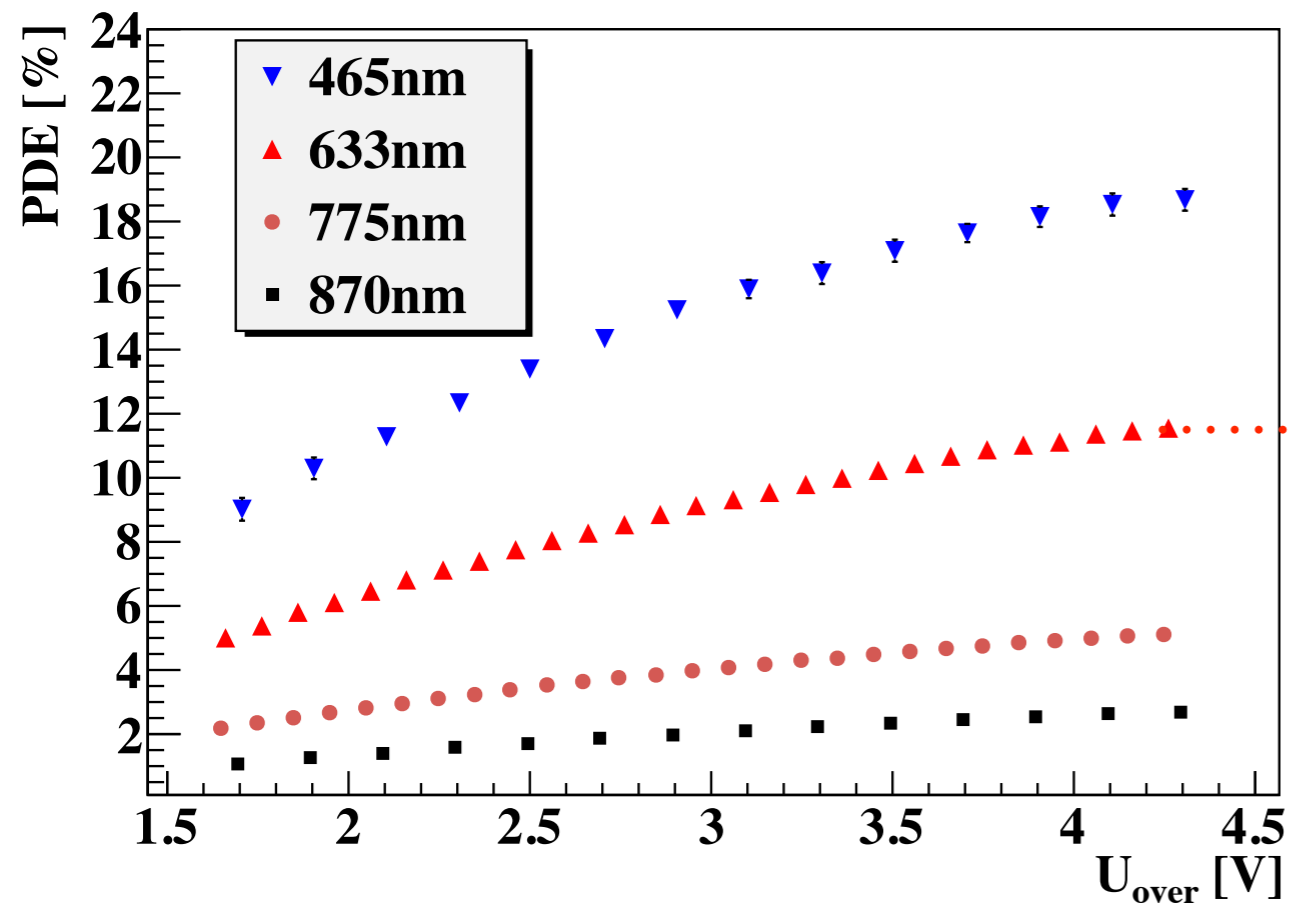
Scale to max. PDE value measured at 633nm

PDE Scaling



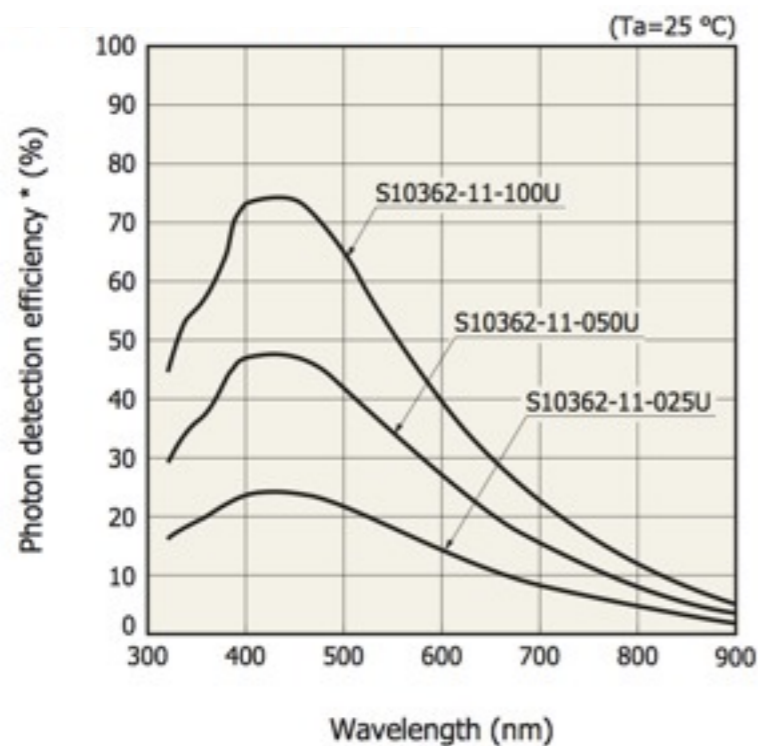
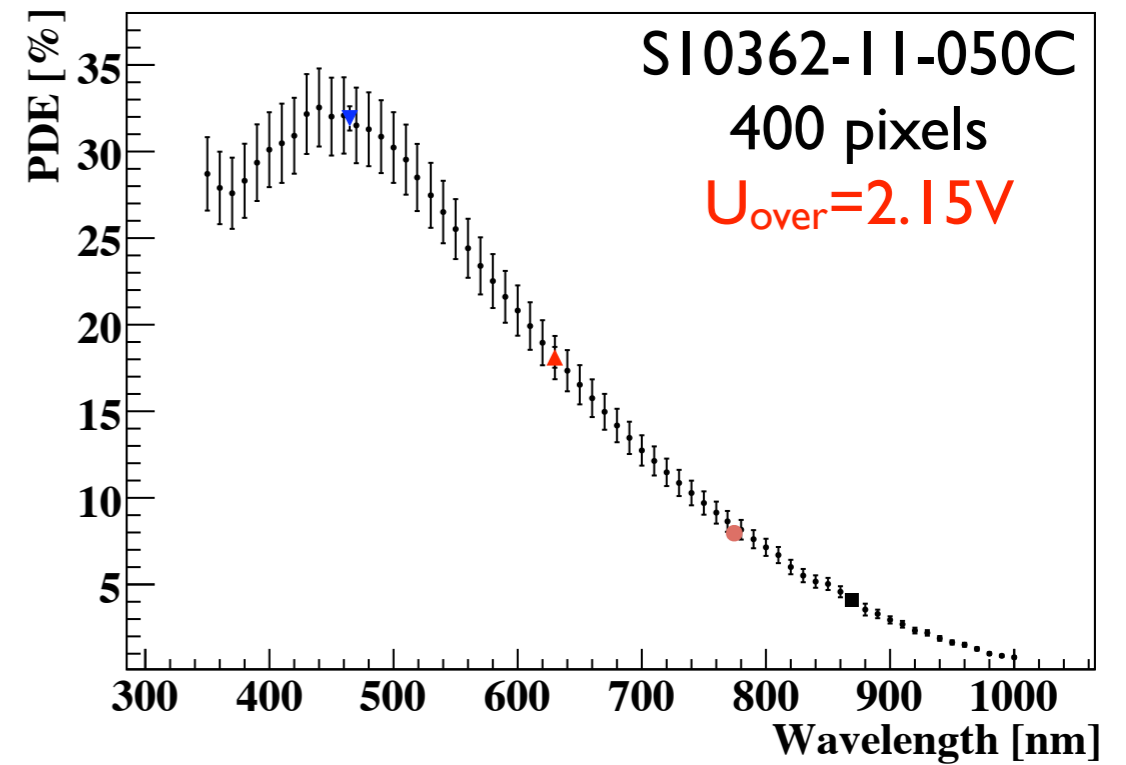
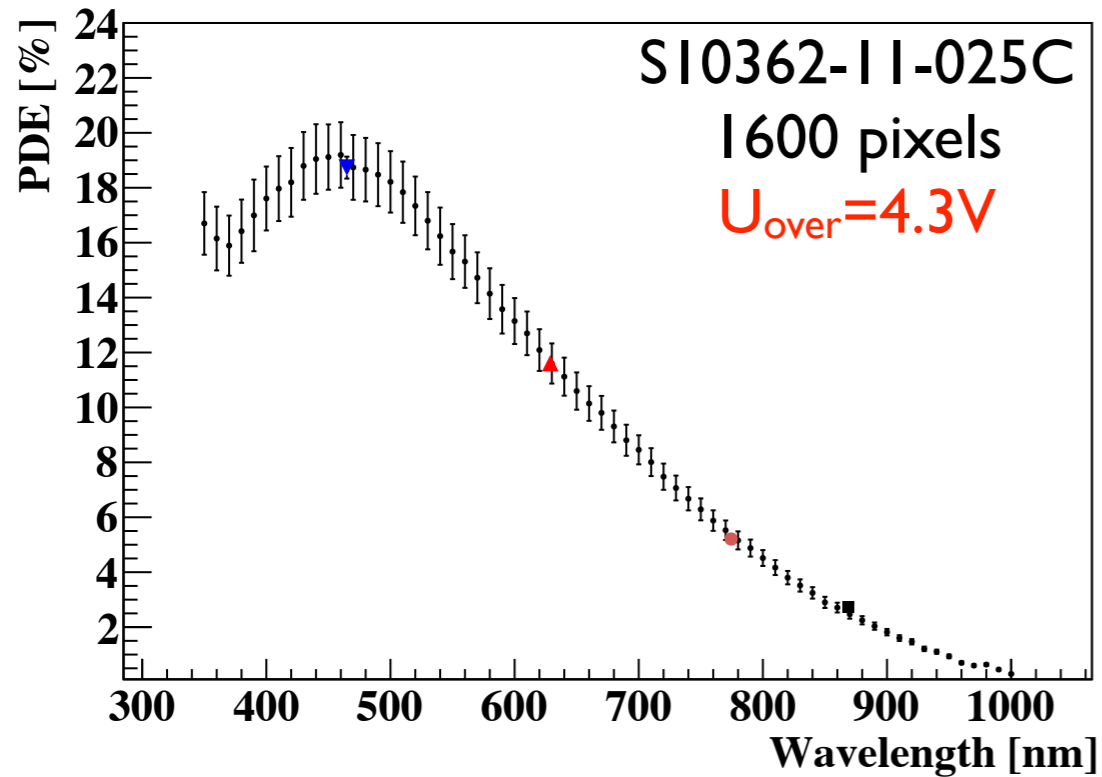
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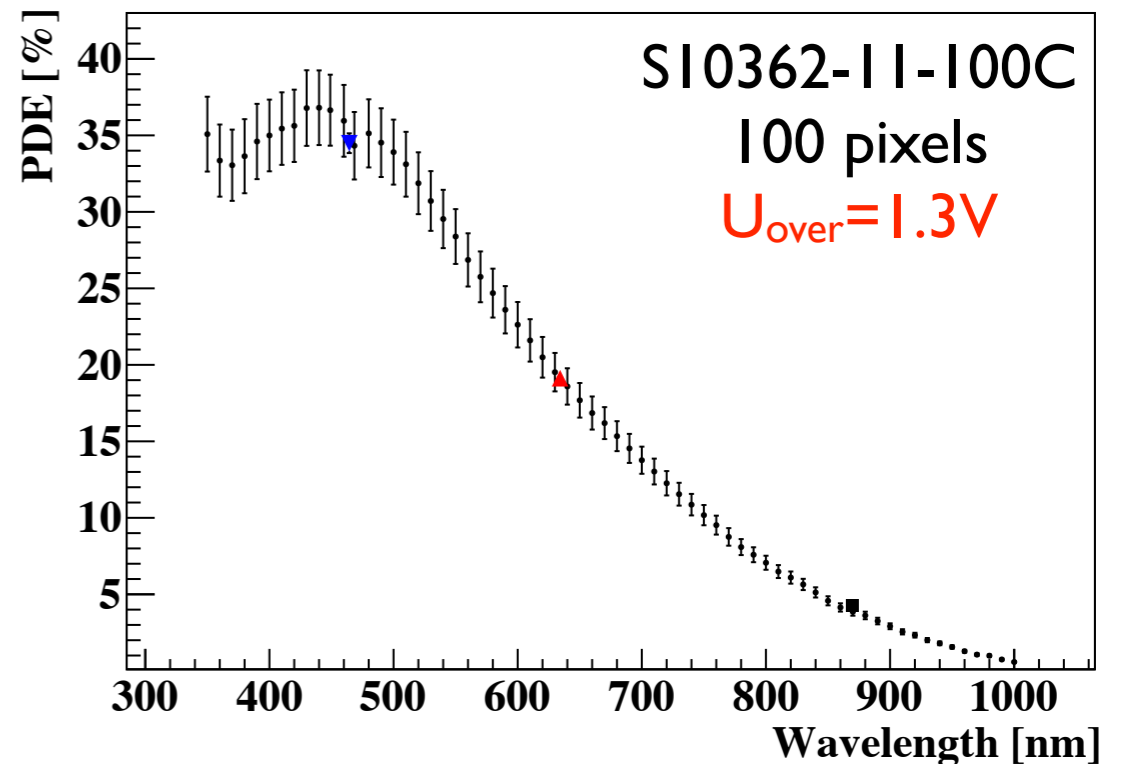


Scale to max. PDE value measured at 633nm

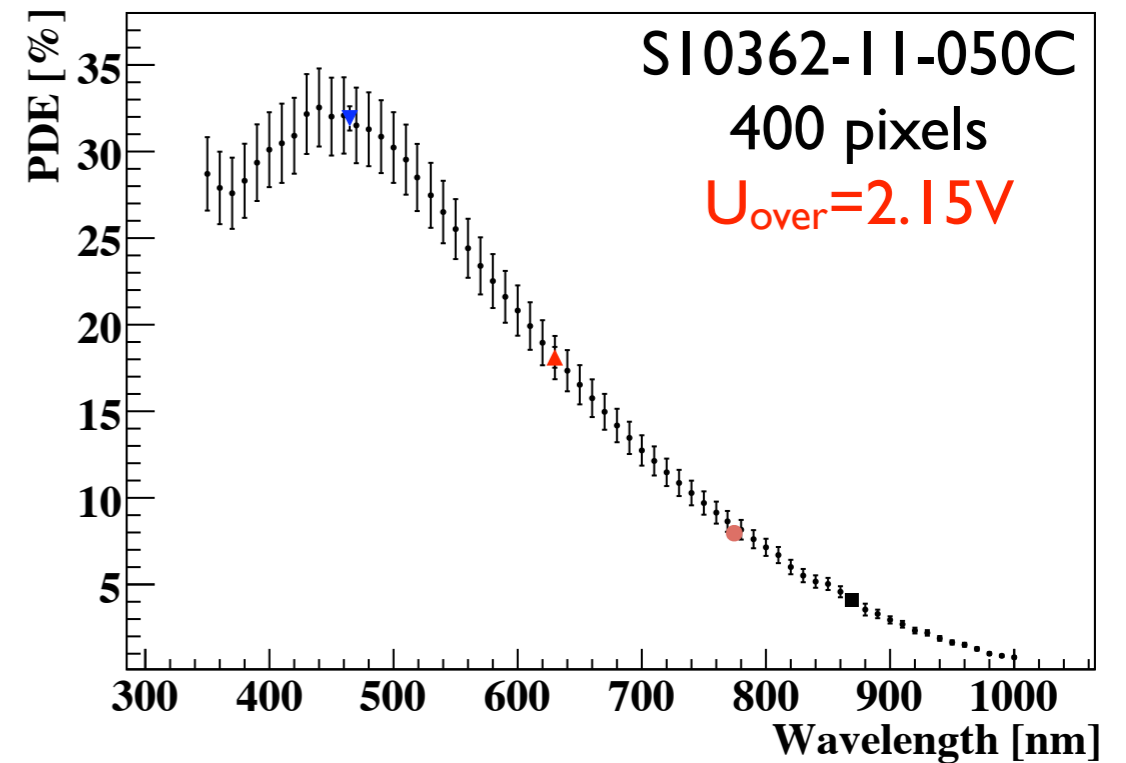
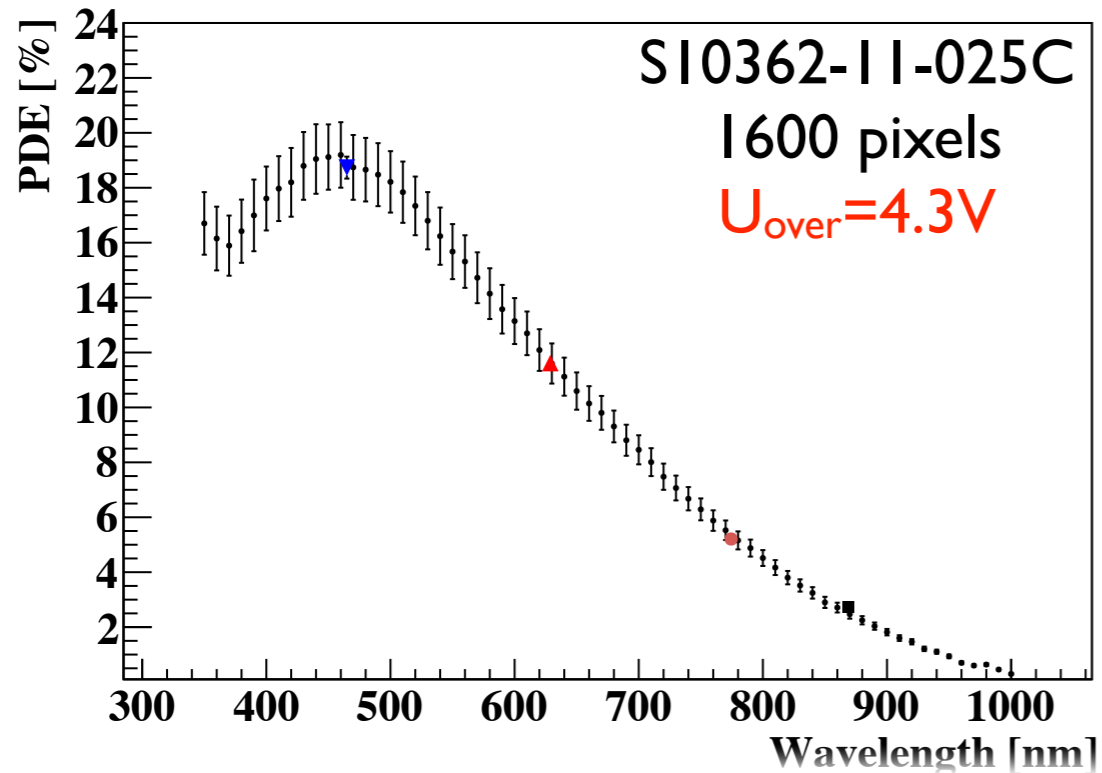
PDE Results: MPPPC



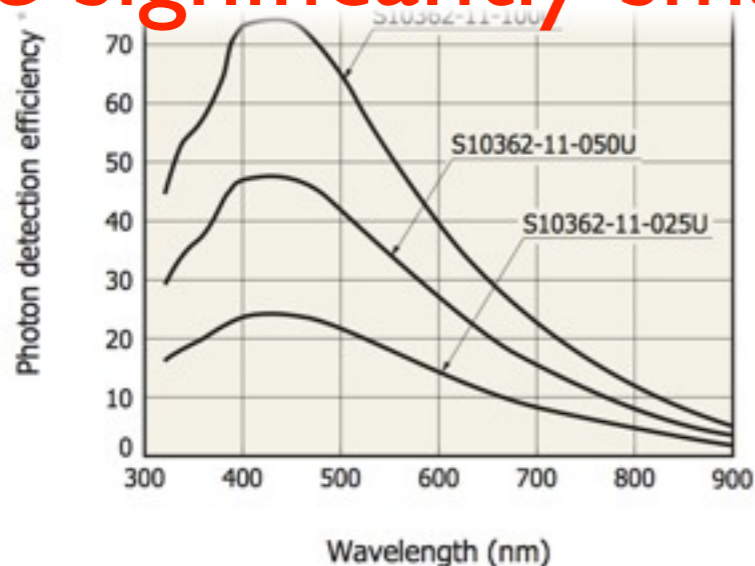
* Photon detection efficiency includes effects of crosstalk and afterpulses. www.hamamatsu.com



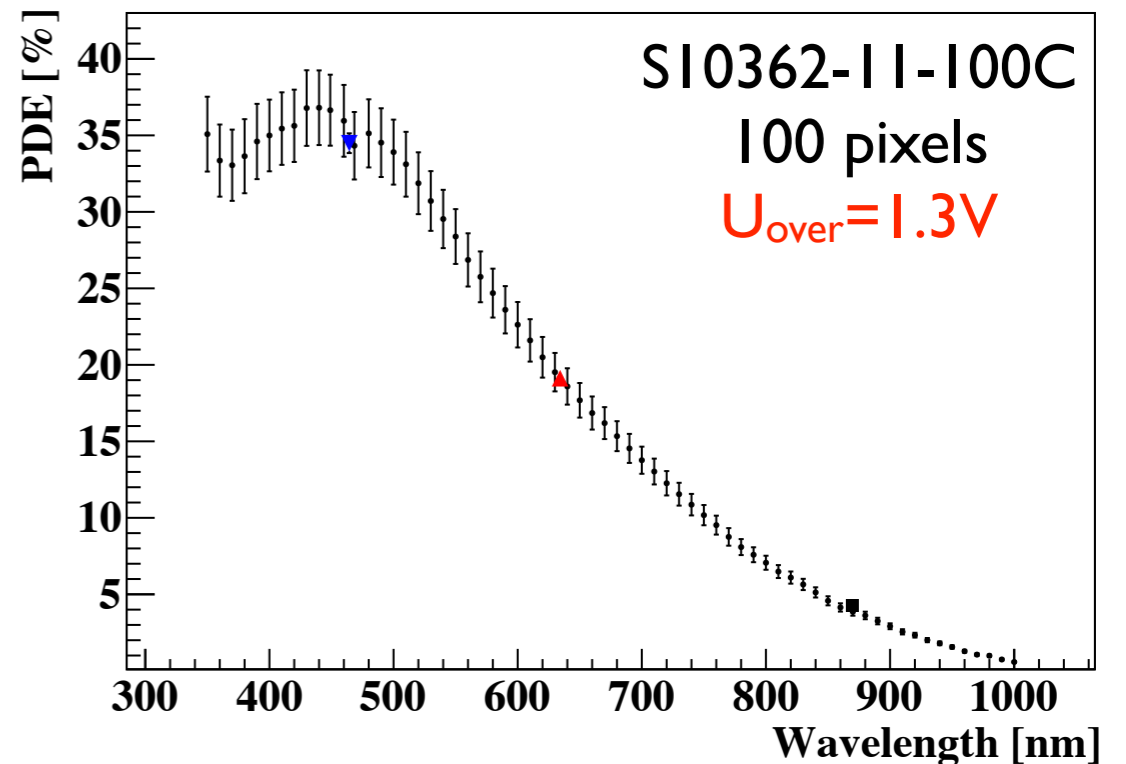
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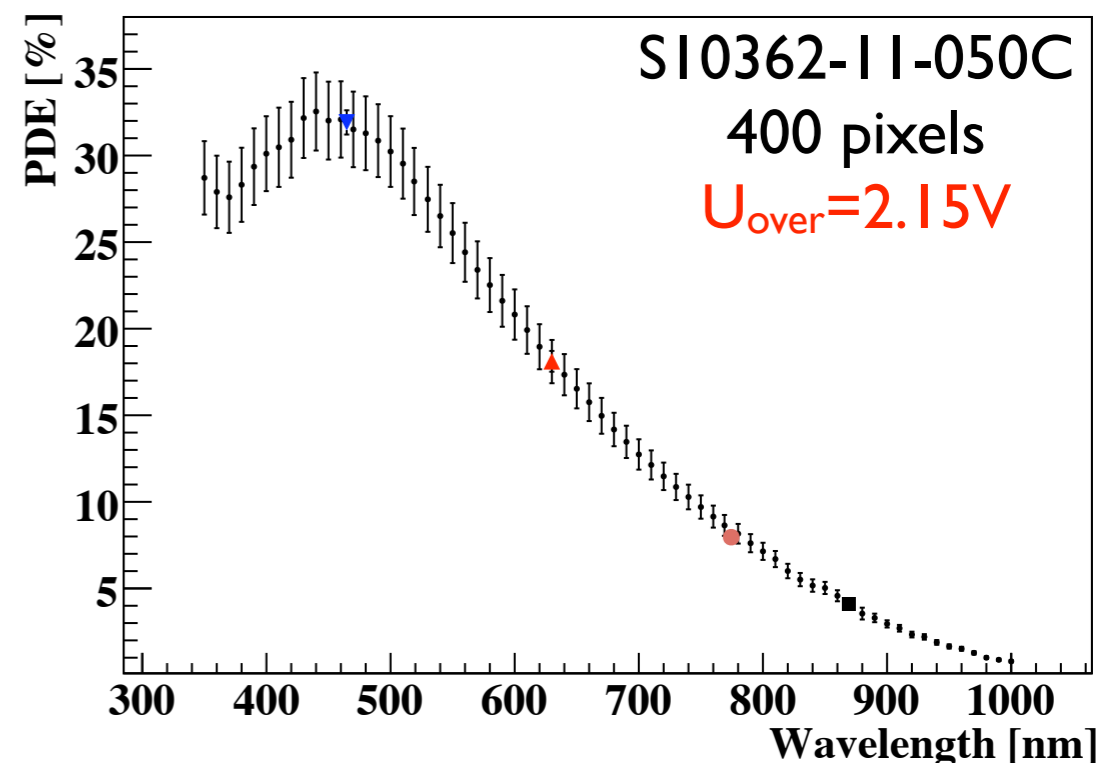
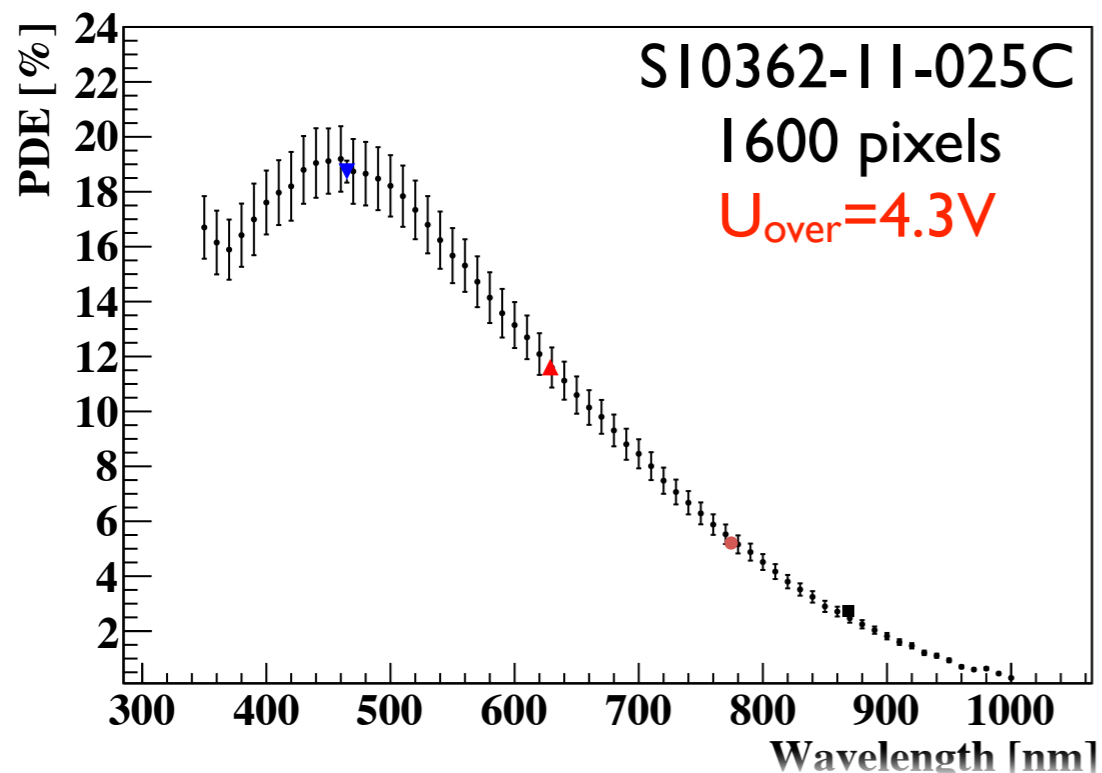
Measured PDE values are significantly smaller.



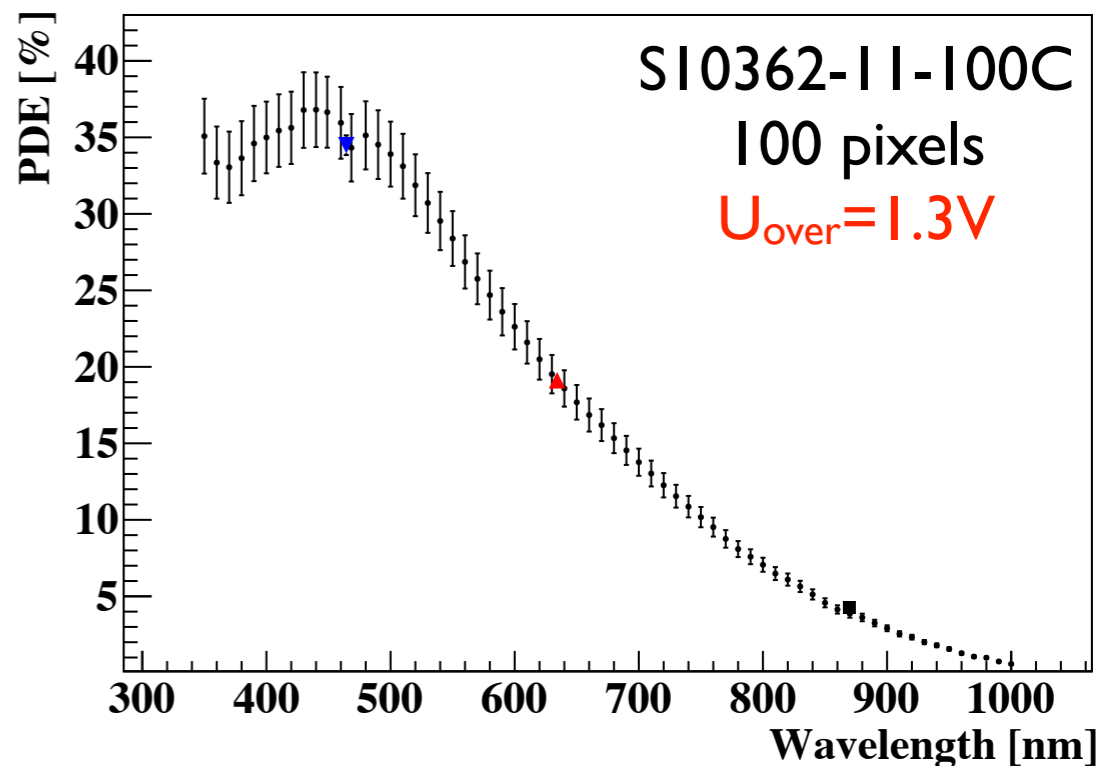
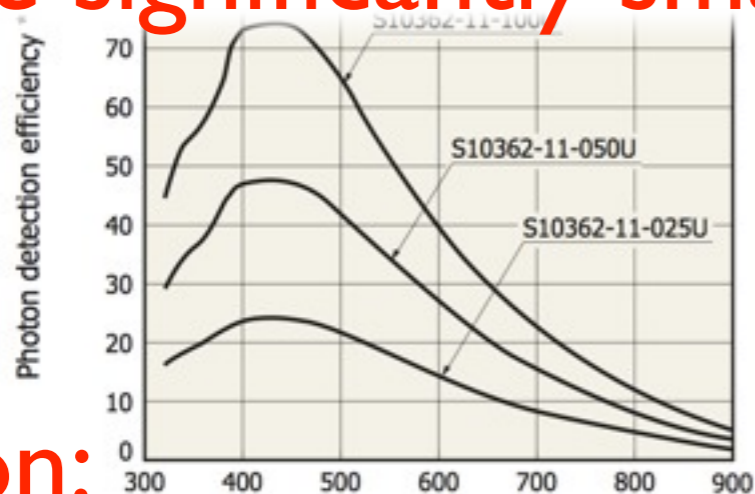
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PDE Results: MPPPC



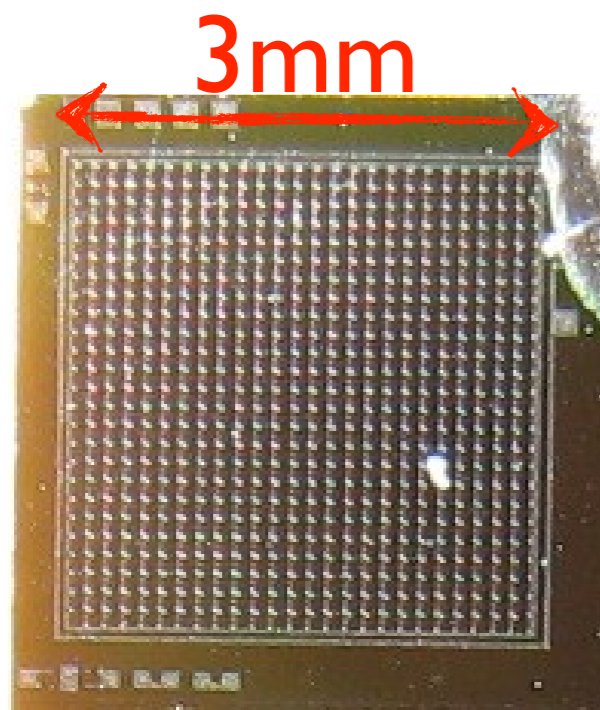
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Reason:

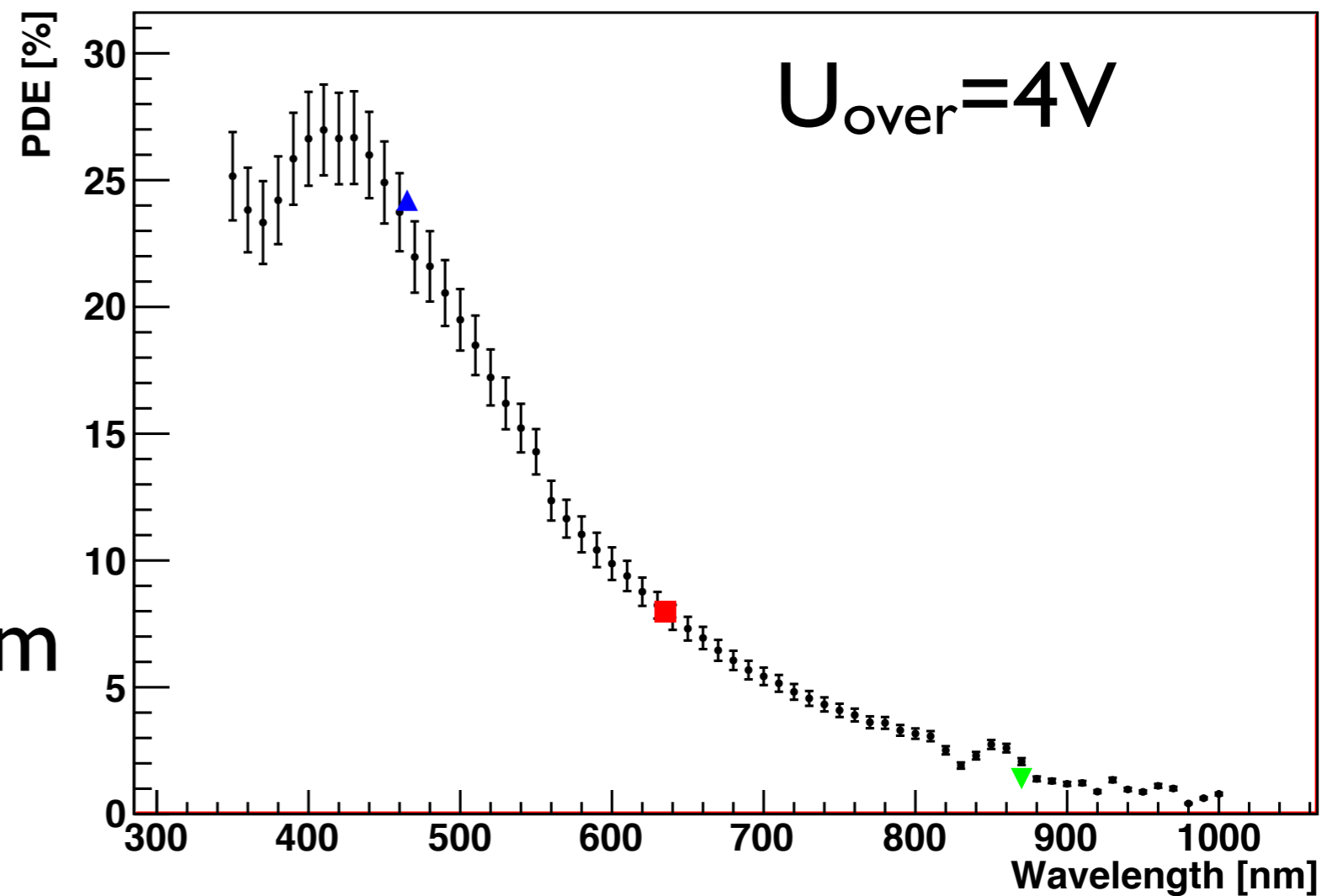
* Photon detection efficiency includes effects of crosstalk and afterpulses.

PDE Results: KETEK



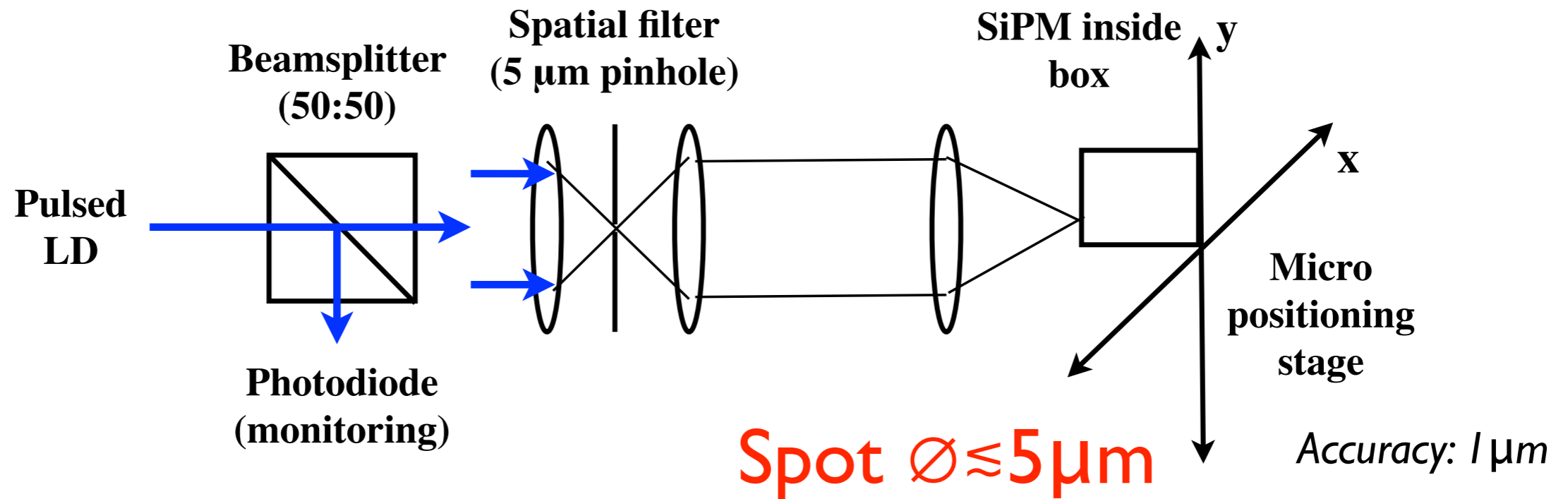
KETEK_3x3mm_UV_35_6V

Highest PDE at ~420nm
blue/UV sensitive

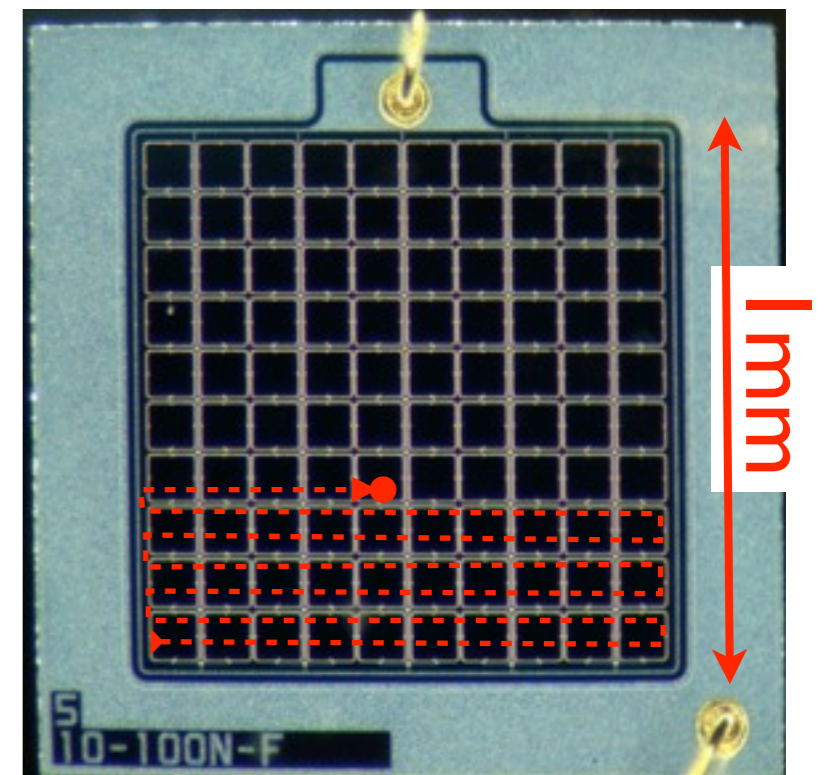


Uniformity Scans

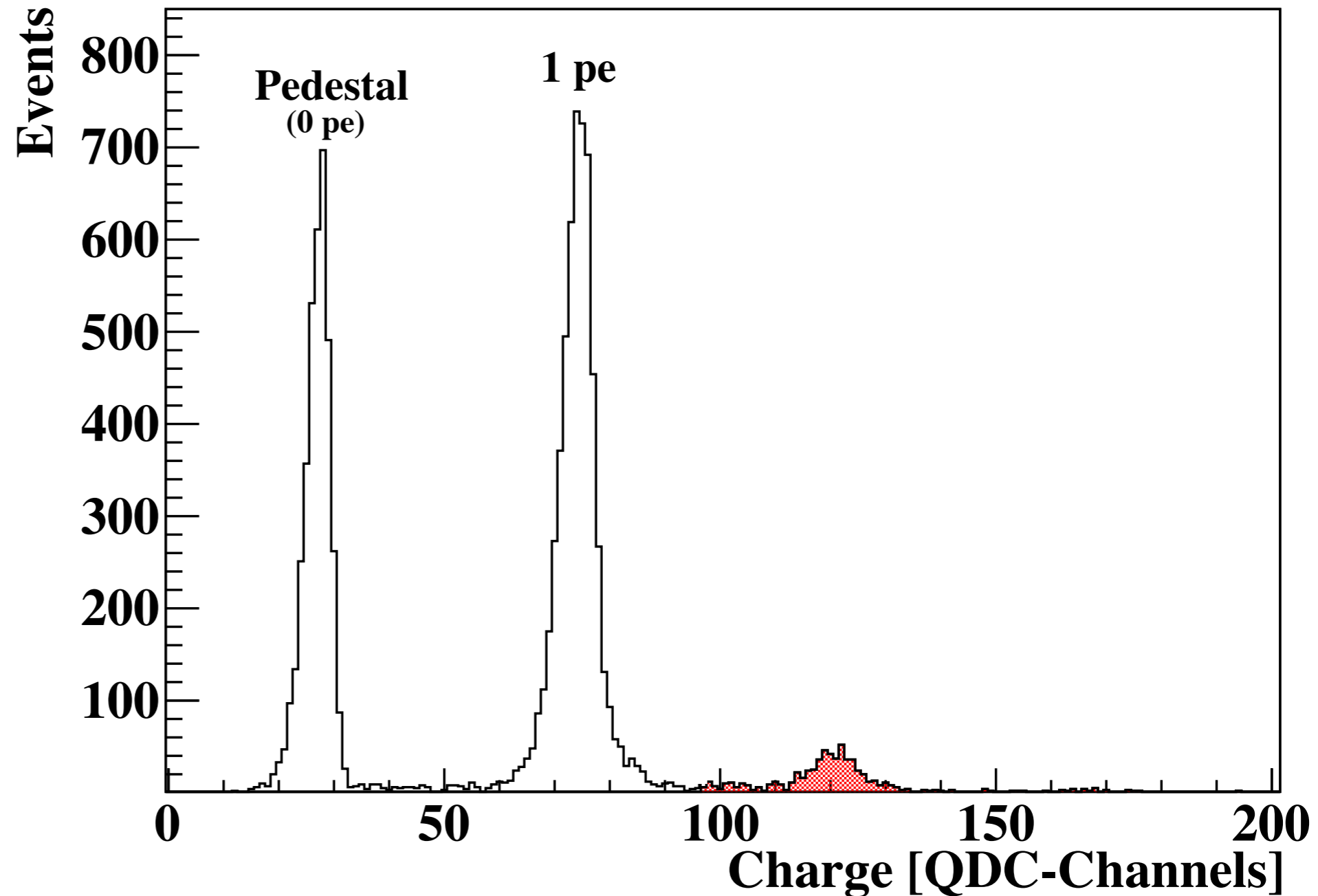
Setup



- Move spot over SiPM surface
- QDC readout (30ns gate)
10,000 events per geom. position
- 3 μm step size \Rightarrow 123,000 positions
- Total time (1 \times 1mm²): \approx 100h



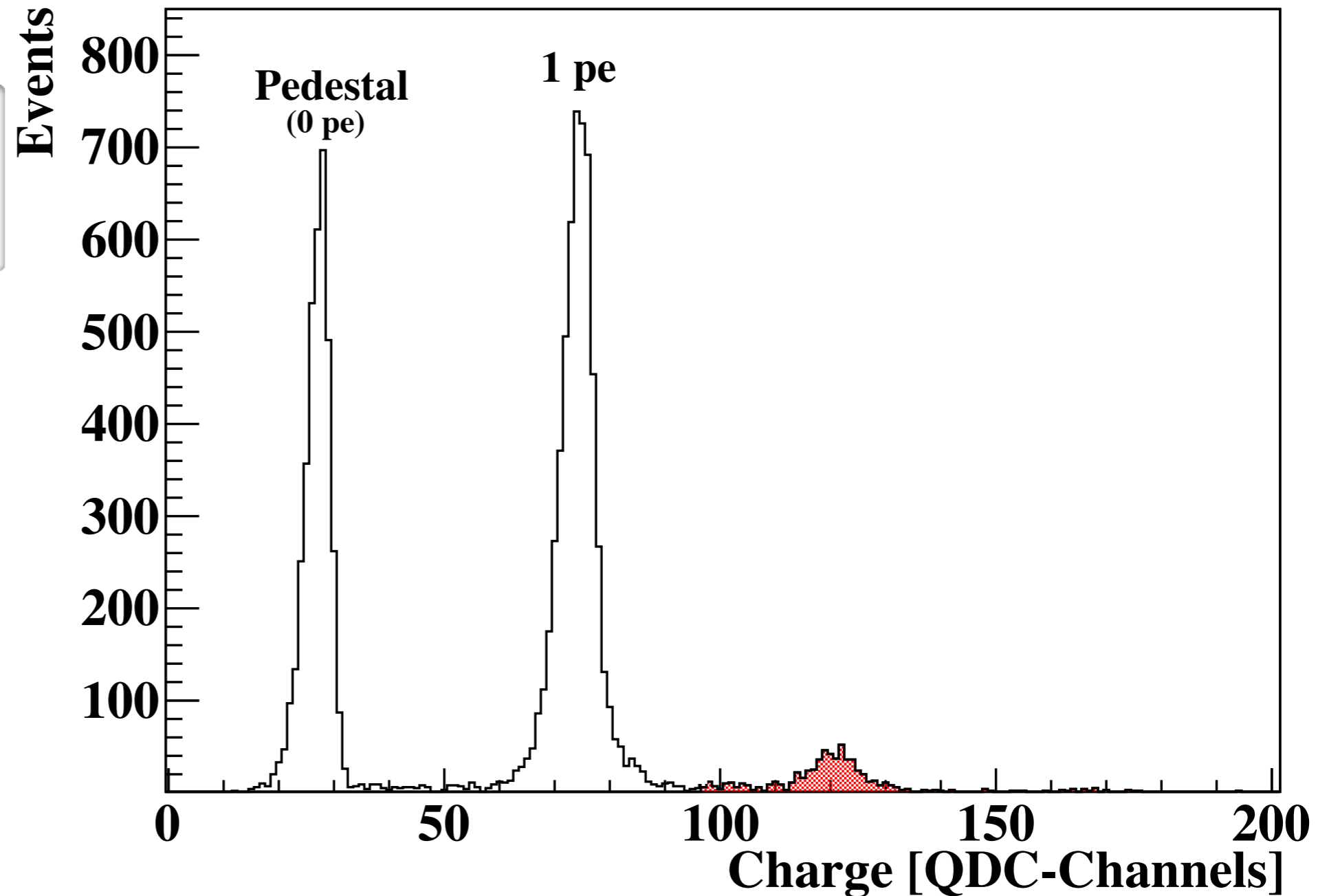
Single Pixel Spectrum



Single Pixel Spectrum

Sensitivity

$$N_{pe} = -\ln \left(\frac{N_{Ped.}}{N_{Tot.}} \right)$$

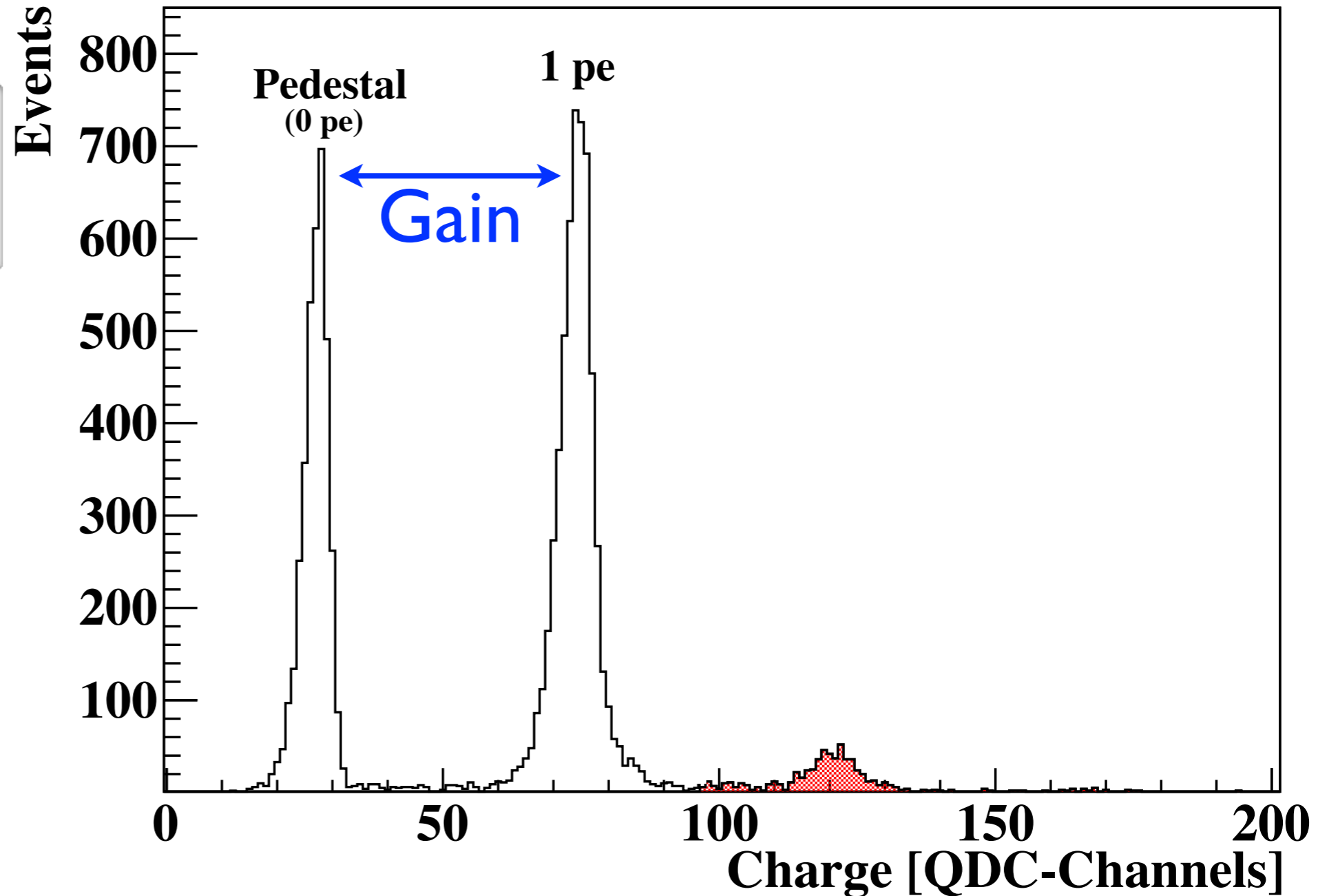


Single Pixel Spectrum

Sensitivity

$$N_{pe} = -\ln \left(\frac{N_{Ped.}}{N_{Tot.}} \right)$$

Gain
(peak distance)



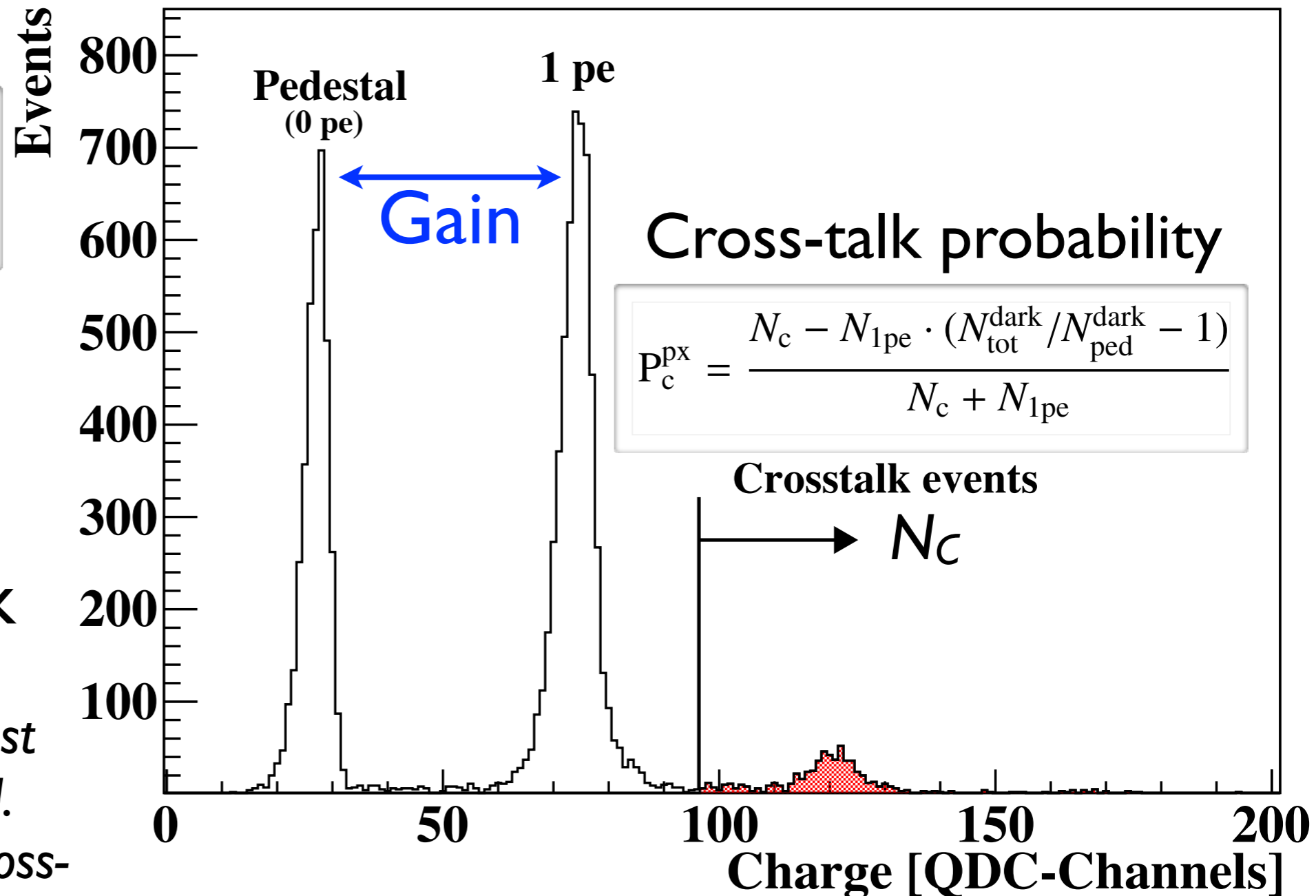
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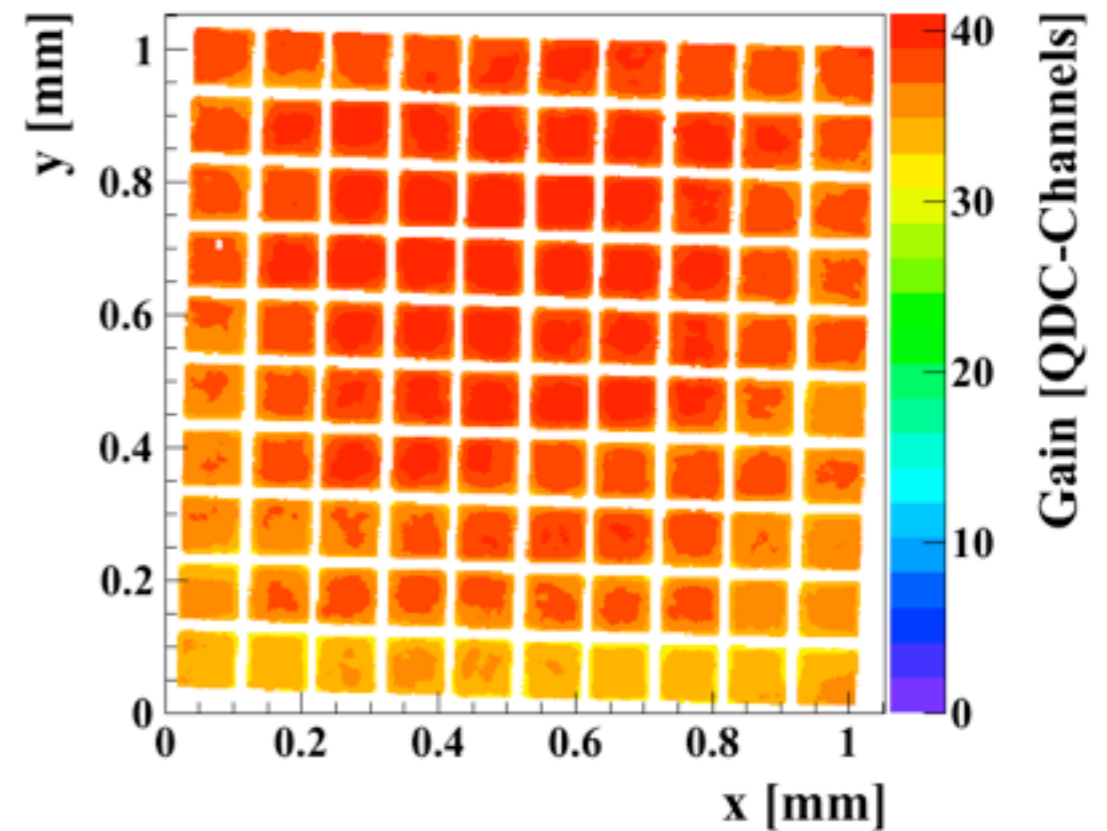
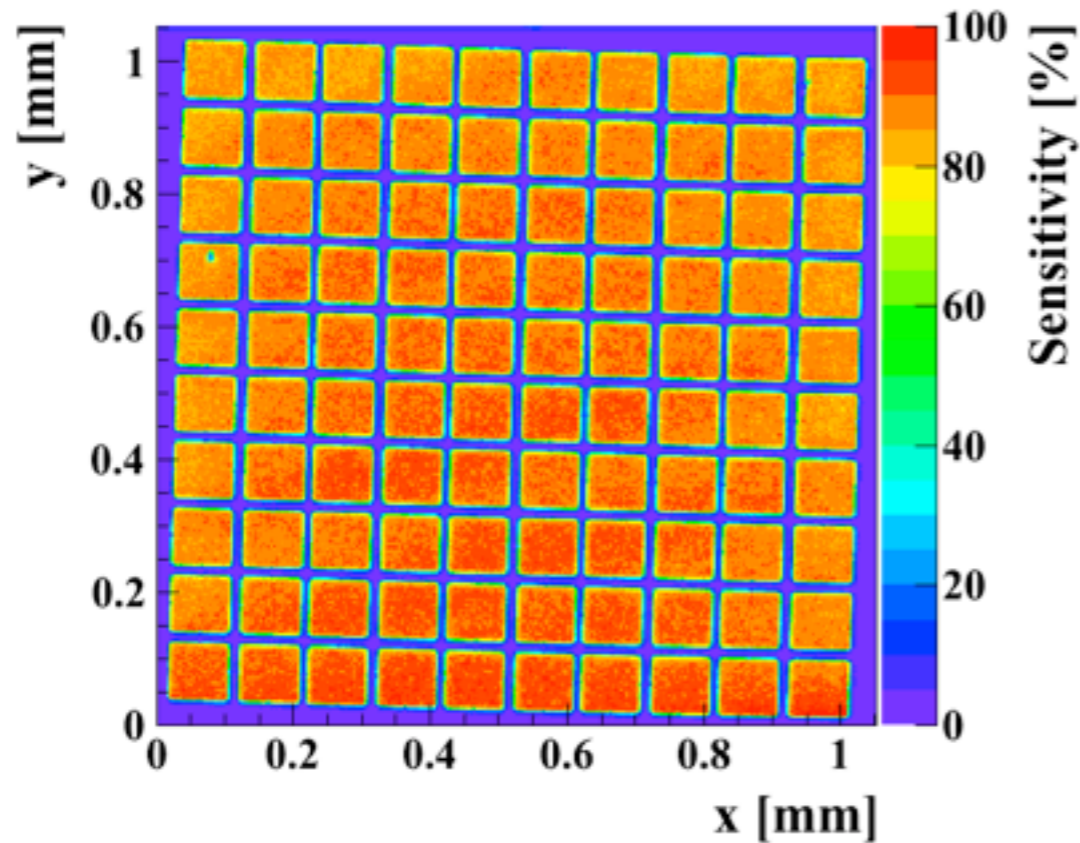
(peak distance)



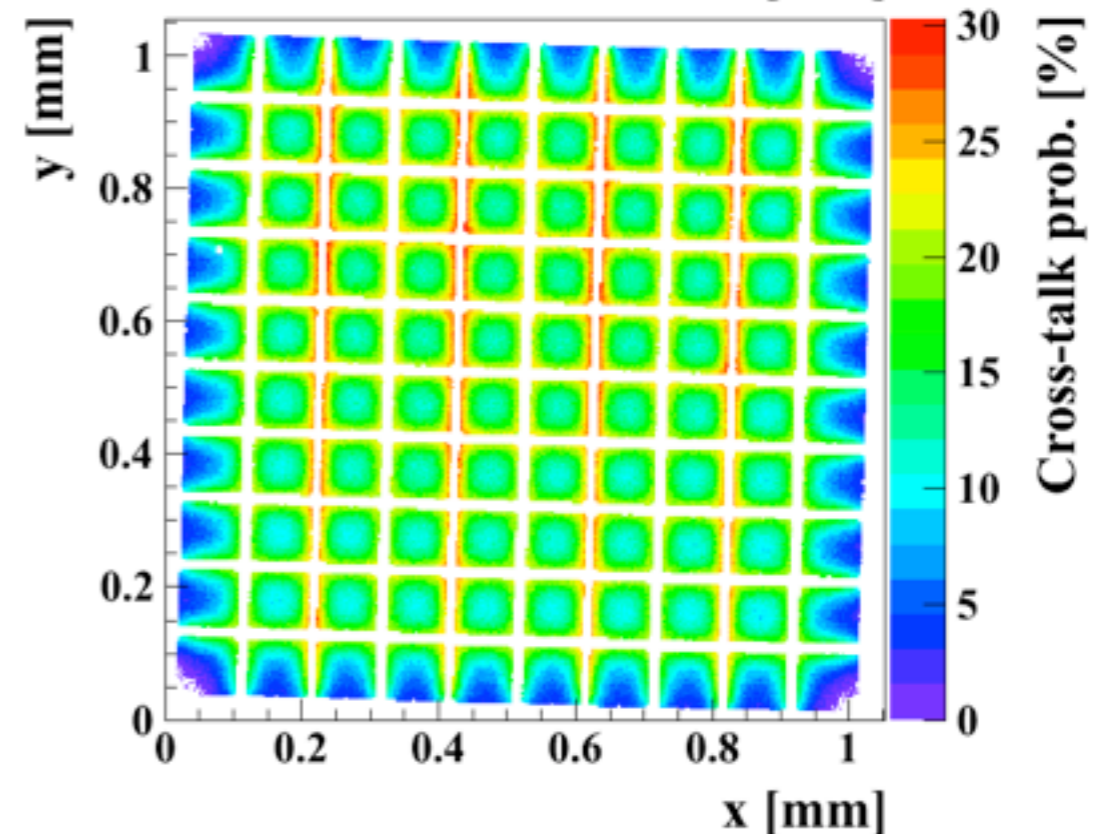
Optical cross-talk

Only single pixel is illuminated, hence at most 1pe events are expected. 2pe events caused by cross-talk

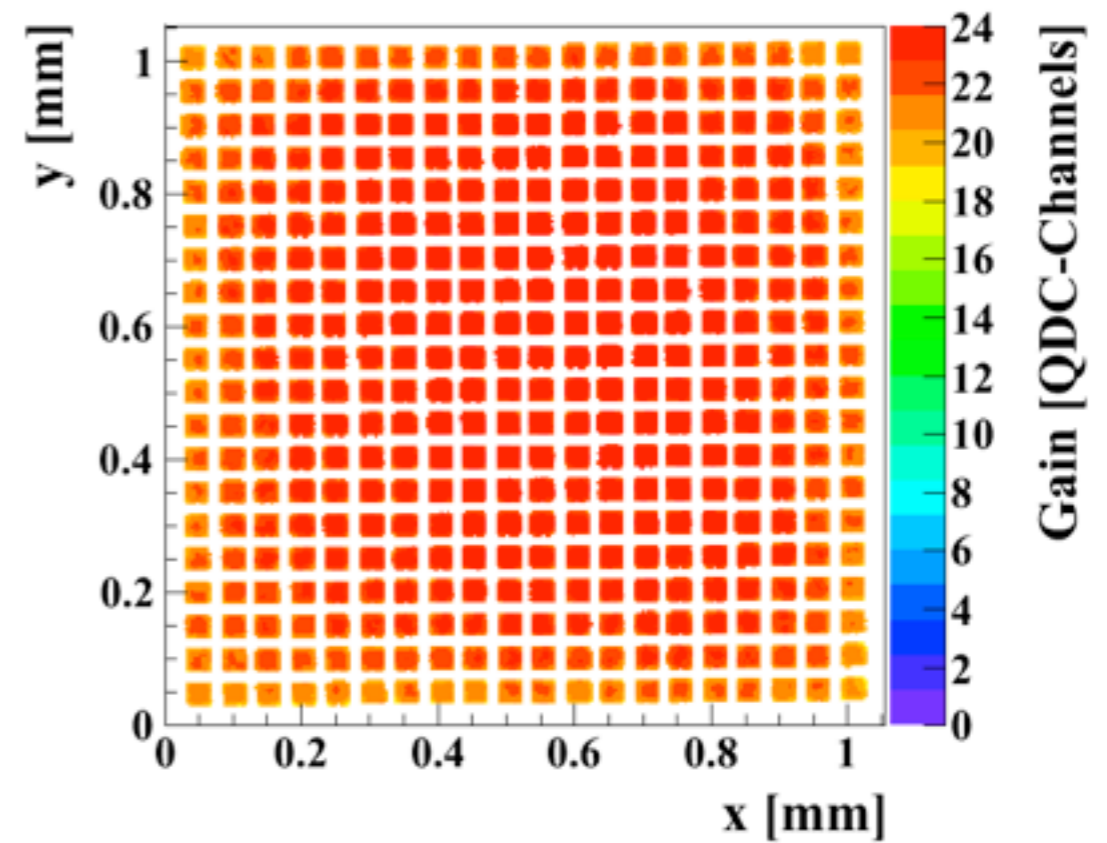
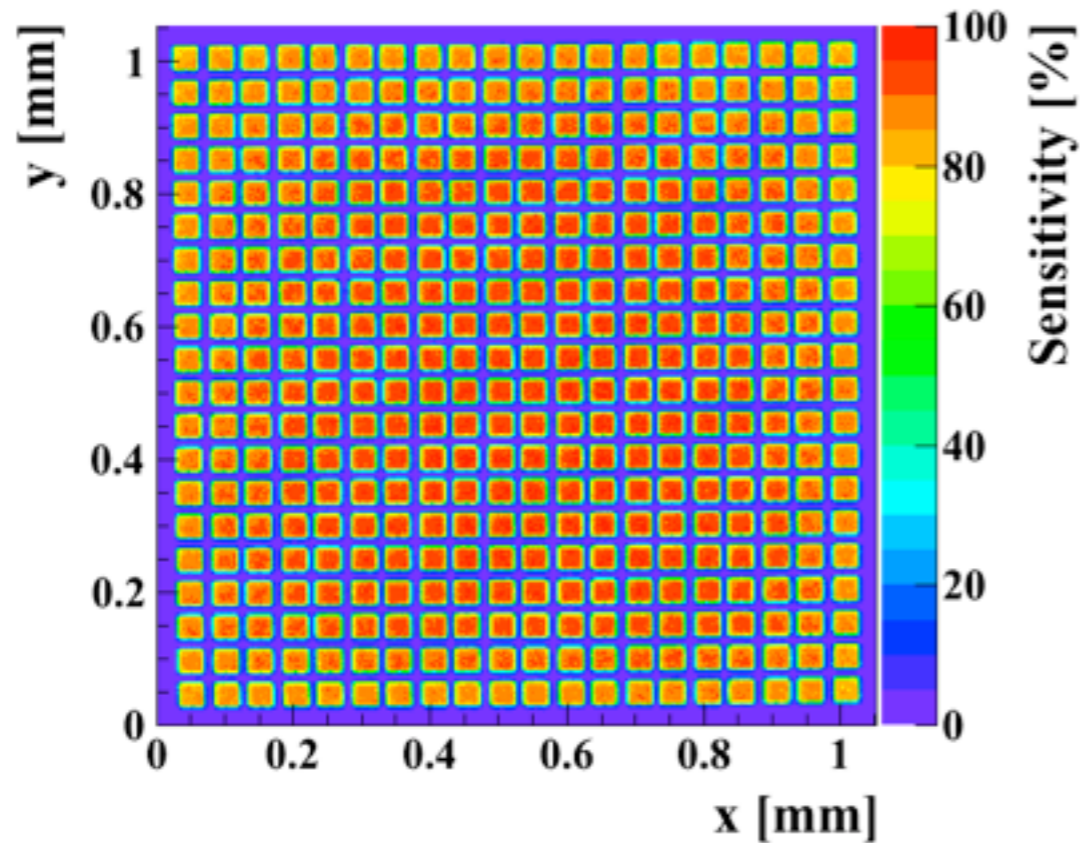
MPPPC 100 pixels



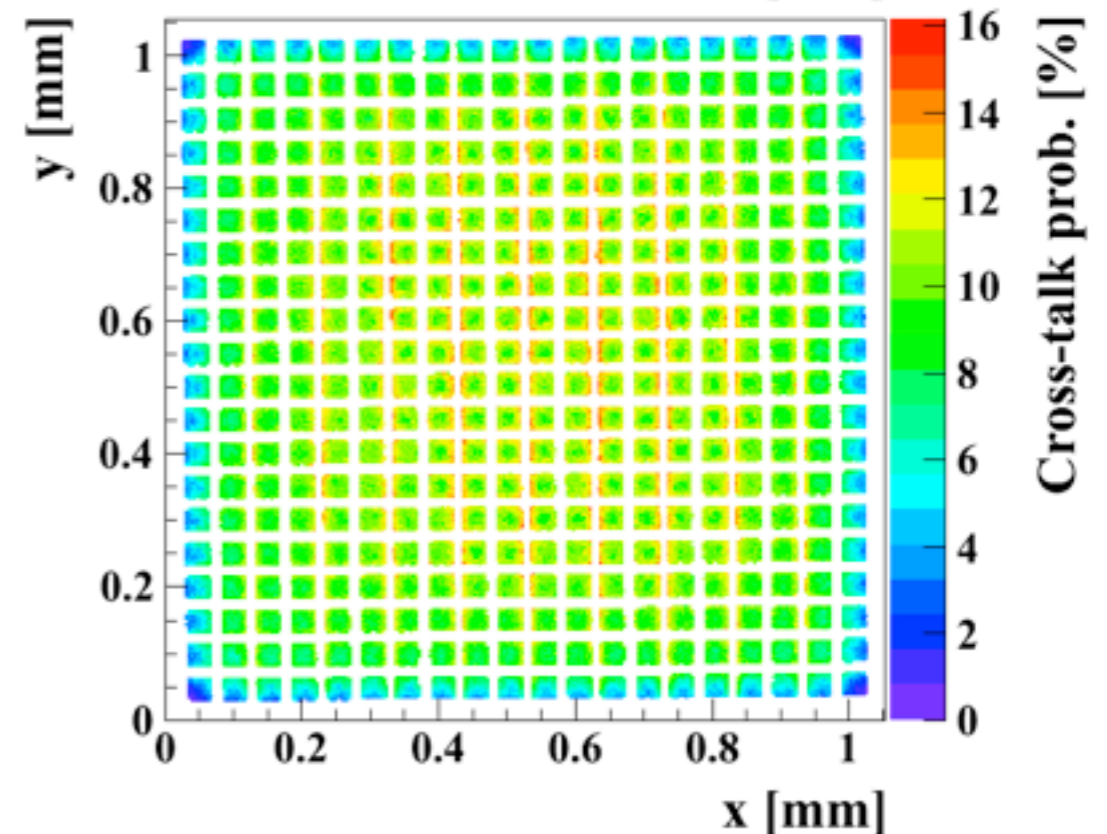
- High uniformity in sensitivity and gain
- Cross-talk shows strong position dependence



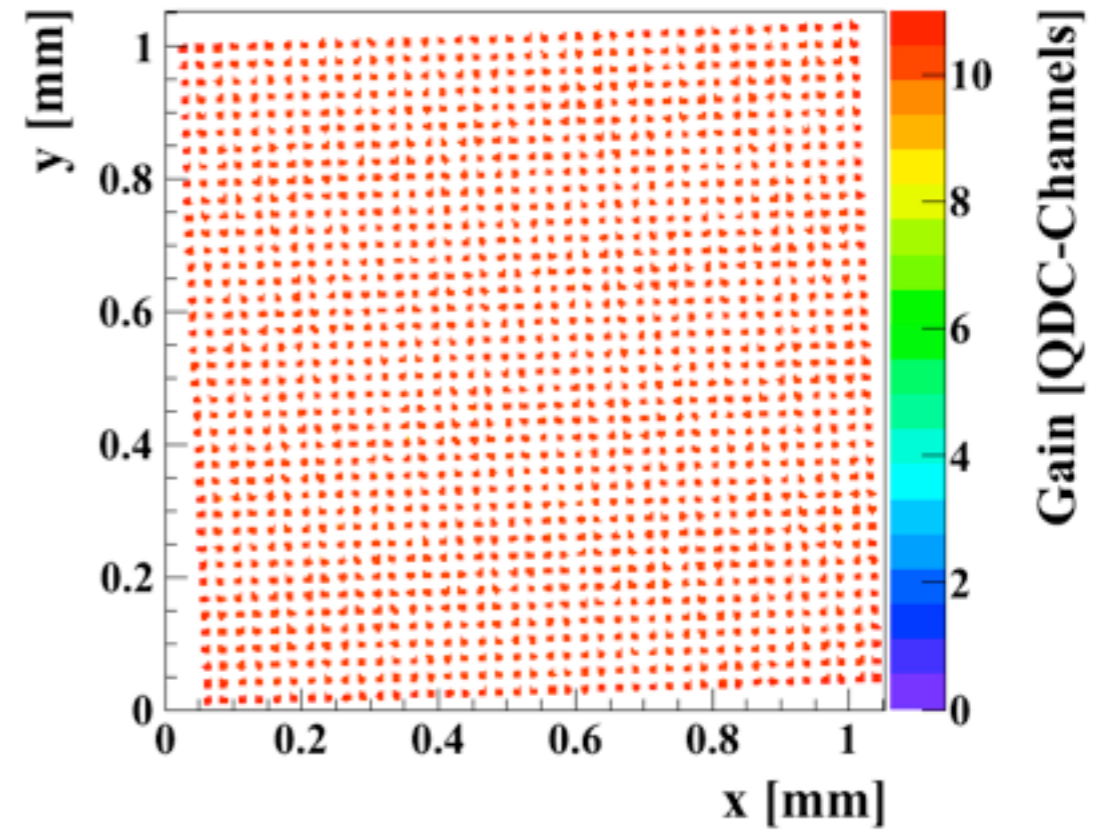
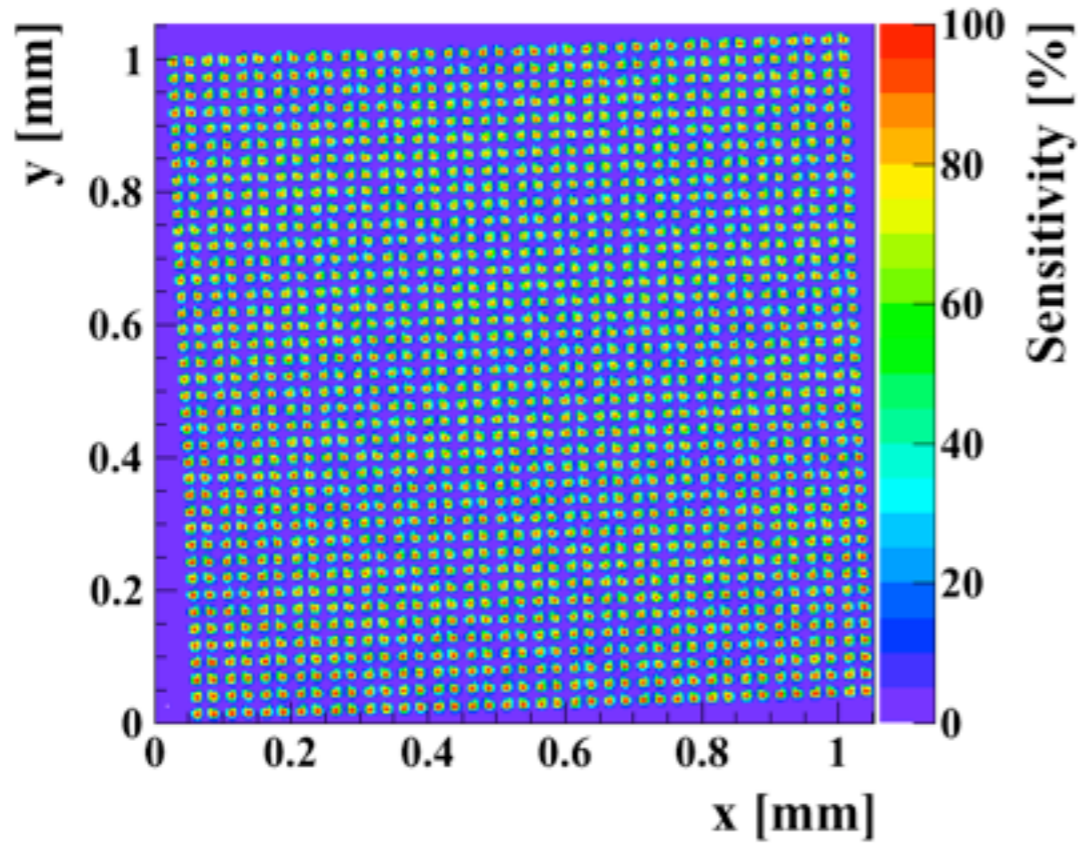
MPPPC 400 pixels



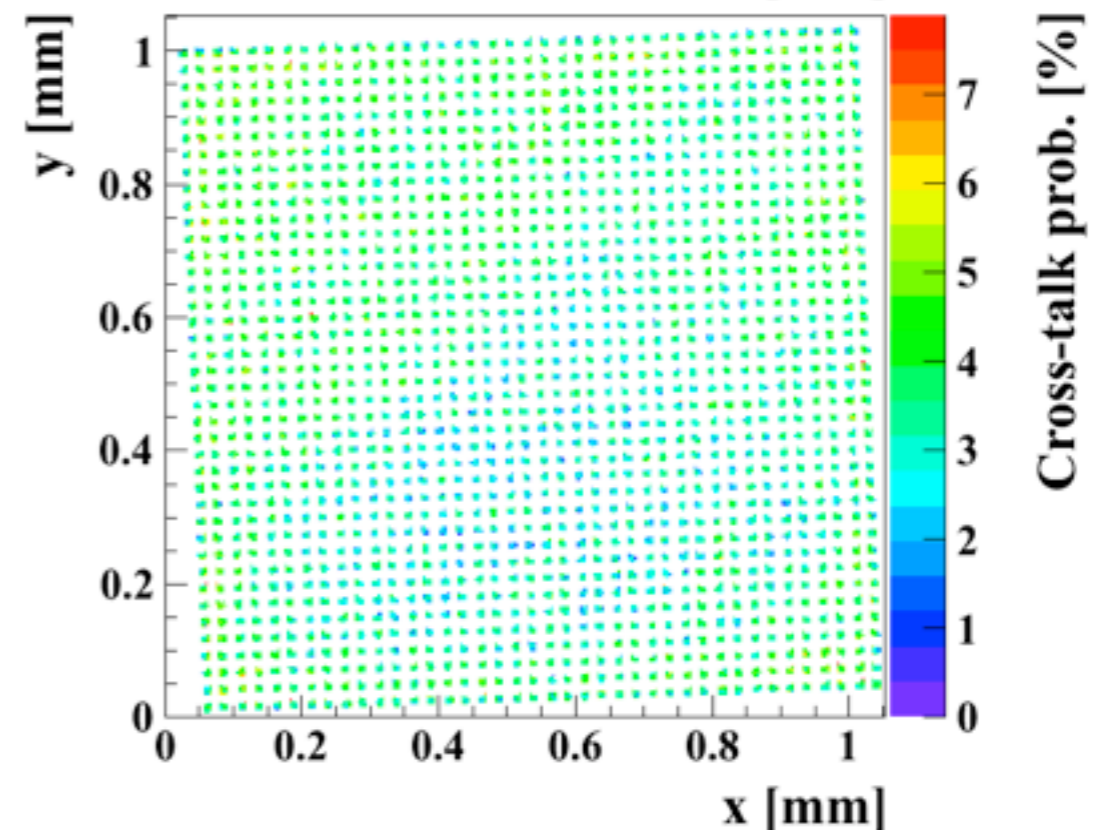
- High uniformity in sensitivity and gain
- Cross-talk shows strong position dependence



MPPPC 1600 pixels



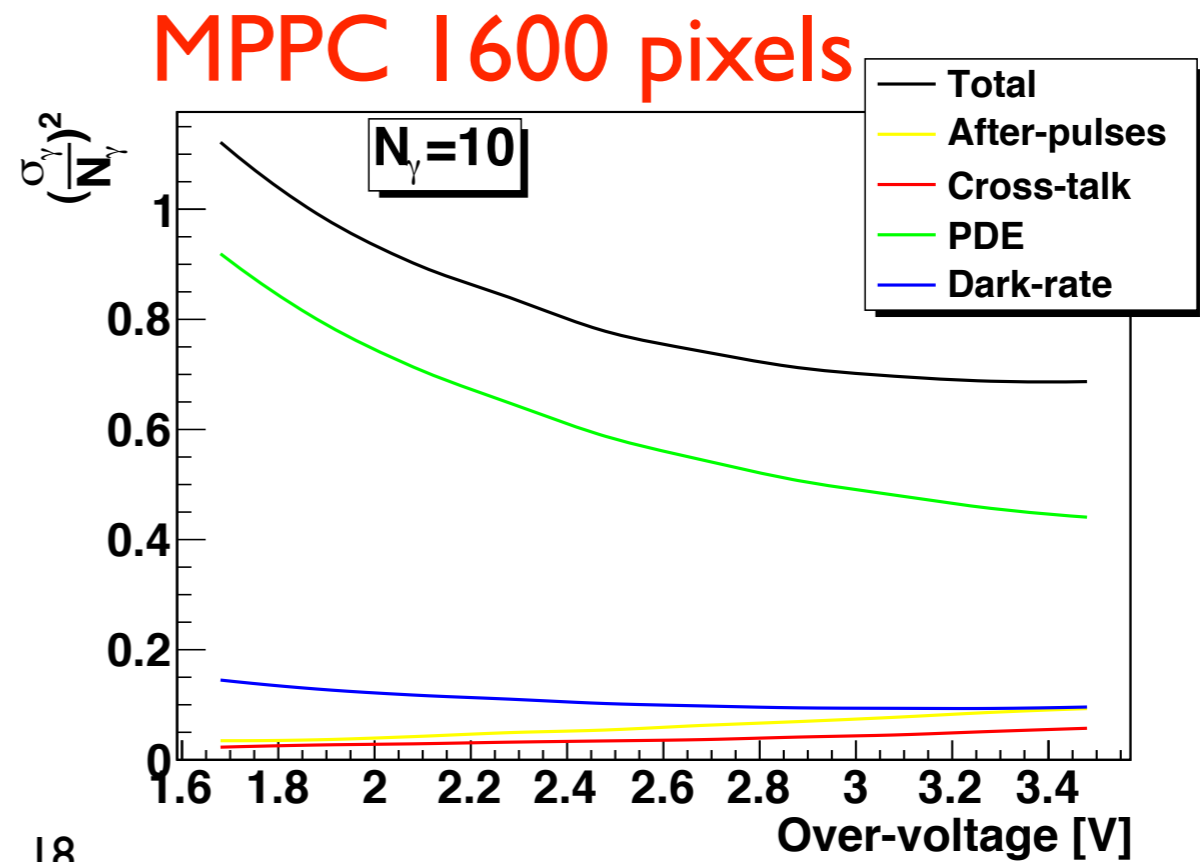
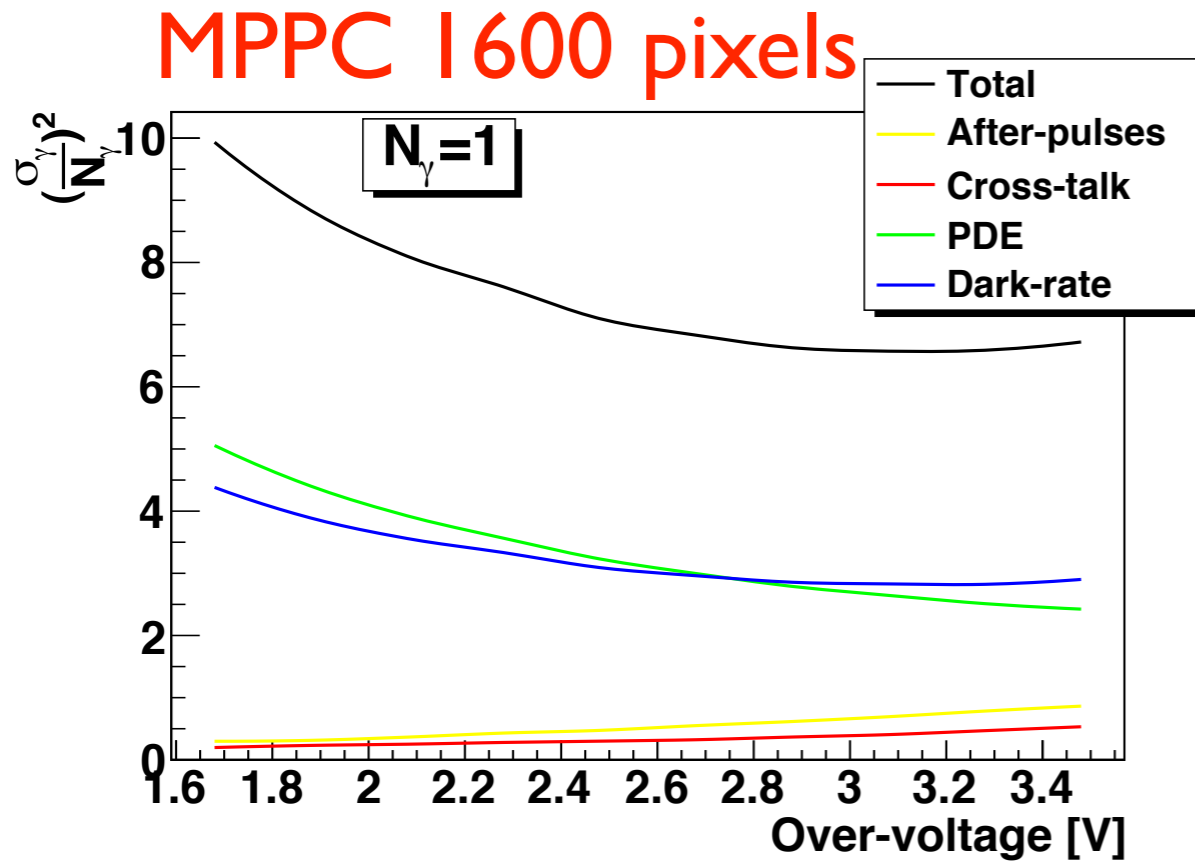
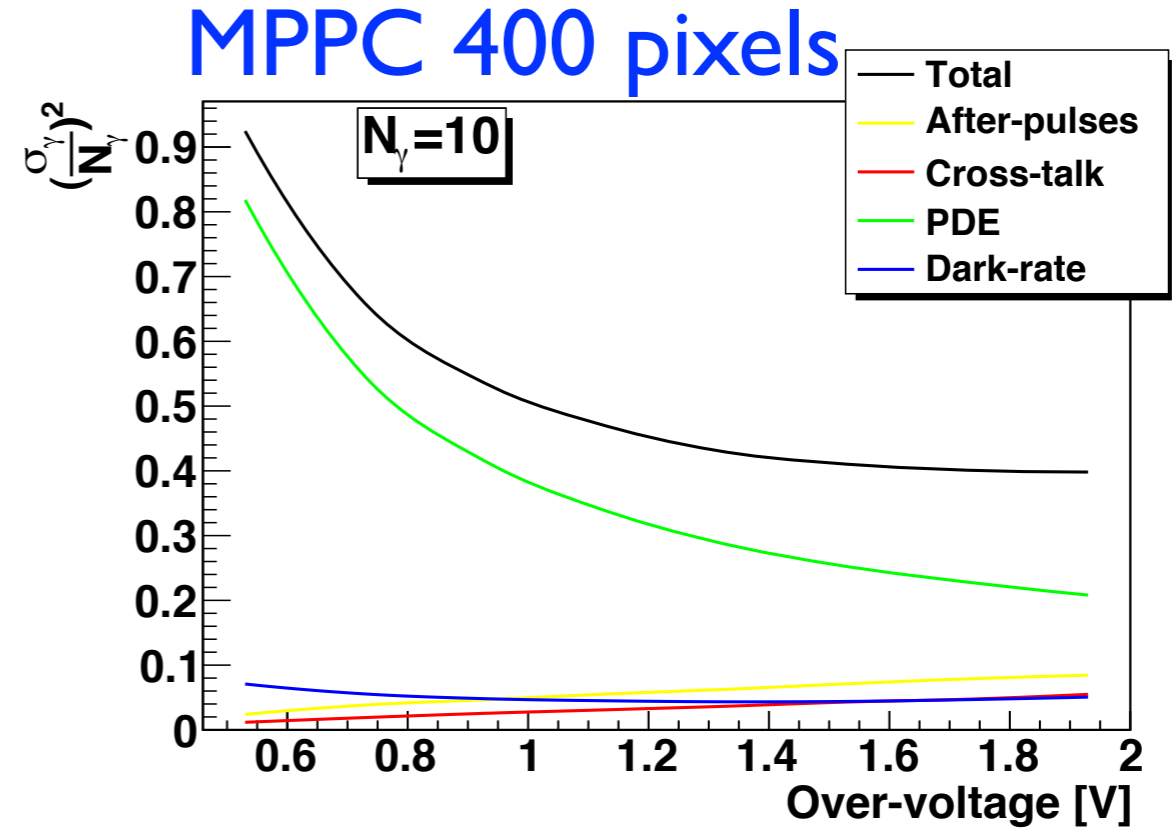
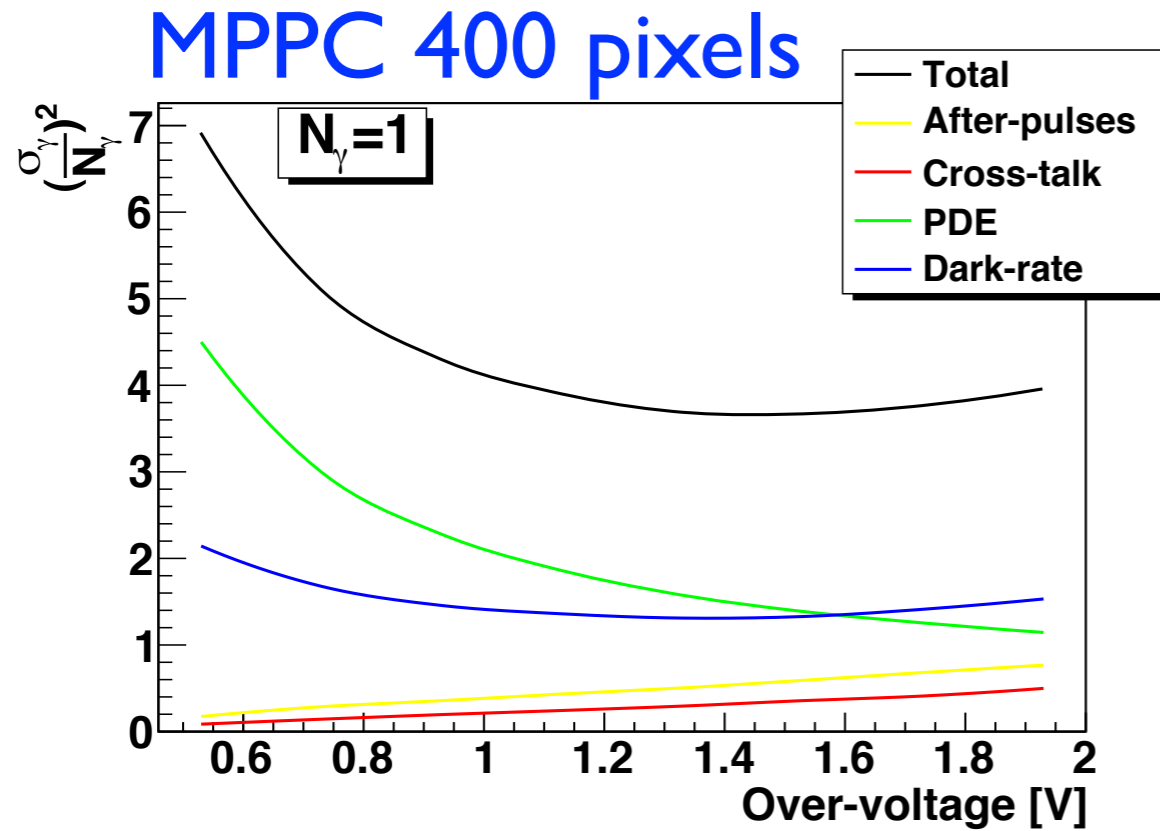
- High uniformity in sensitivity, gain and cross-talk probability



Photon Counting Resolution

*Combining the results of PDE, dark-rate, cross-talk
and after-pulse measurements*

Results



Summary

- Test stand for SiPM measurements has been established
- Complete characterization
- Dark-rate, cross-talk, after-pulse prob.
- Temperature dependence
- Photon detection efficiency (350 - 1000nm)
- Photon counting resolution
- Uniformity scans

Backup

Photon Counting

PDE (binomial)

$$B_{PDE}(N_{PDE}) = \binom{N_\gamma}{N_{PDE}} PDE^{N_{PDE}} \cdot (1 - PDE)^{N_\gamma - N_{PDE}}$$

$$\langle N_{PDE} \rangle = N_\gamma \cdot PDE \quad \sigma_{N_{PDE}} = \sqrt{N_\gamma \cdot PDE(1 - PDE)}$$

Cross-talk, after-pulses (binomial)

$$\sigma_{N_{CT}} = \sqrt{(\langle N_{PDE} \rangle + \langle N_{DR} \rangle) \cdot P_{CT}(1 - P_{CT})}$$

$$\sigma_{N_{AP}} = \sqrt{(\langle N_{PDE} \rangle + \langle N_{DR} \rangle) \cdot P_{AP}(1 - P_{AP})}$$

Dark-rate (Poisson)

$$\langle N_{DR} \rangle = DR \cdot \Delta t$$

$$\sigma_{N_{DR}} = \sqrt{DR \cdot \Delta t}$$

$$\Delta t = 300 \text{ ns}$$

$$\frac{\sigma_{N_\gamma}}{N_\gamma} = \frac{\sigma_{N_{Signal}}}{N_\gamma \cdot PDE} = \frac{\sqrt{\sigma_{N_{PDE}}^2 + \sigma_{N_{CT}}^2 + \sigma_{N_{AP}}^2 + \sigma_{N_{DR}}^2}}{N_\gamma \cdot PDE}$$

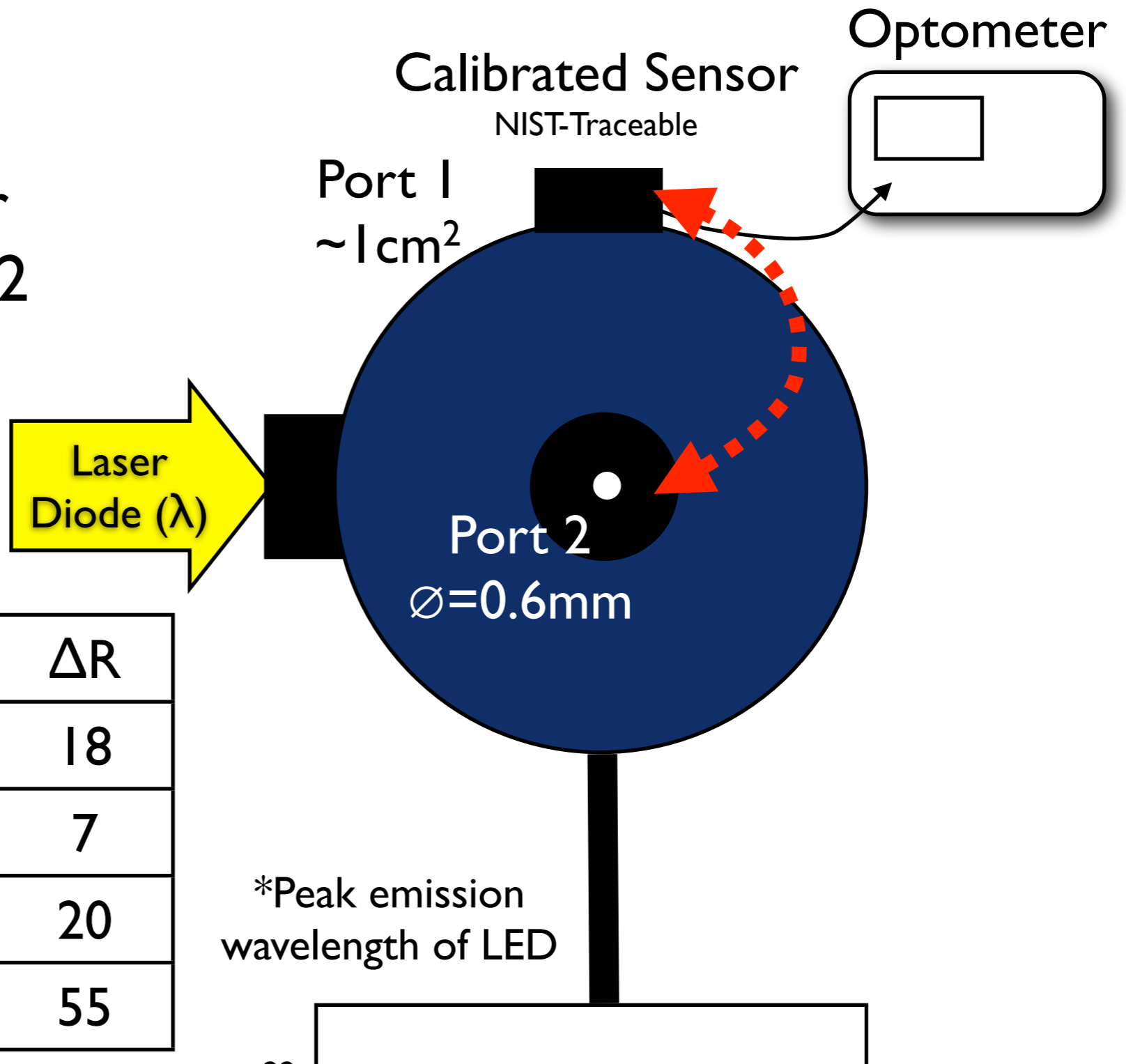
Measurement of Power-ratio R

($\varnothing=0.6\text{mm}$ aperture)

The Power-ratio R is measured by moving the calibrated sensor from port 1 to port 2 and backwards.

$$R = \frac{P_{\text{Port1}}}{P_{\text{Port2}}}$$

Type	λ [nm]	$R_{0.6\text{mm}}$	ΔR
Laserdiode	633	3852	18
Laserdiode	775	4328	7
LED	465*	4200	20
LED	870*	4625	55



Dark-rate Correction

The number of photoelectrons needs to be corrected for the dark-rate.

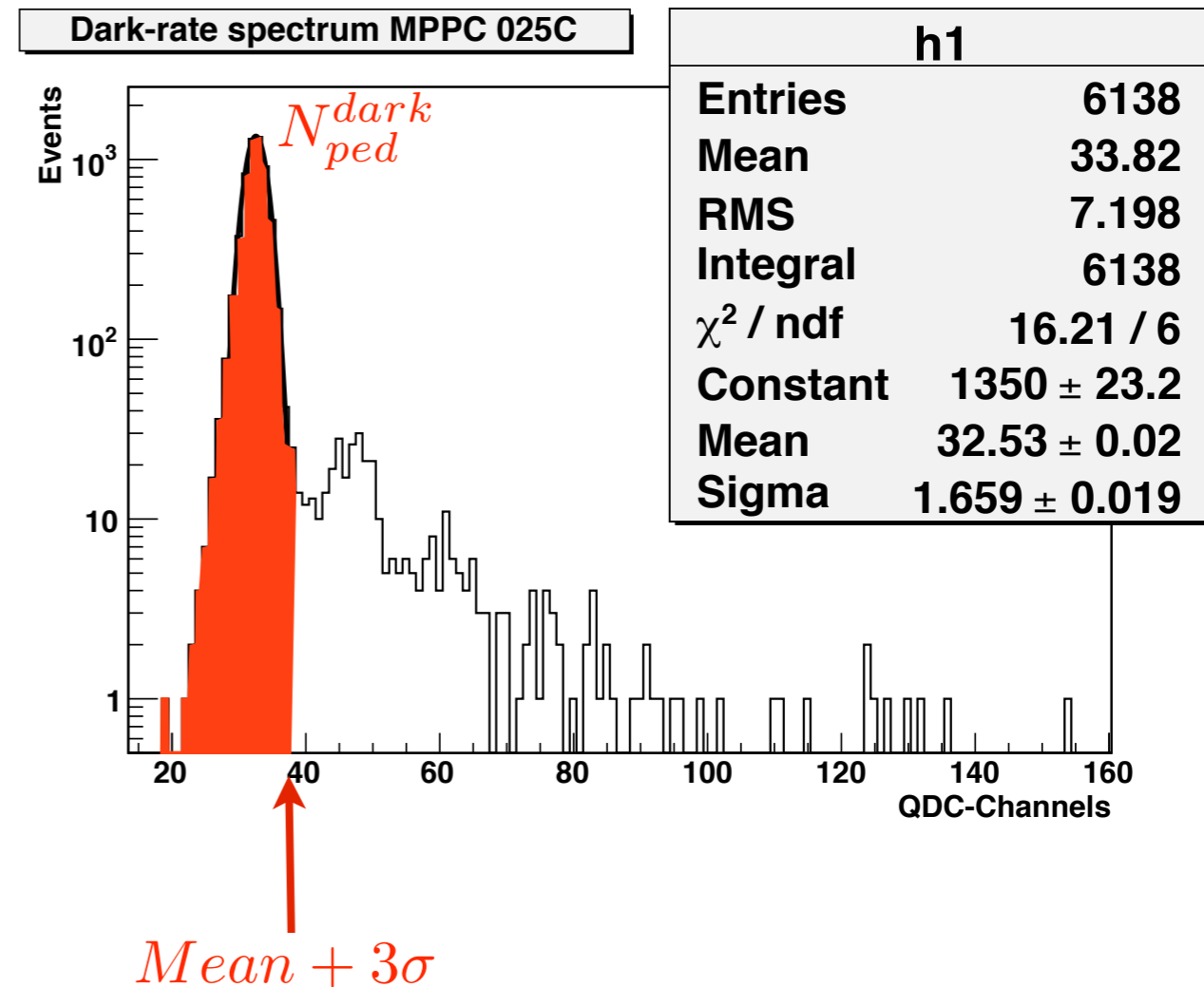
→ Acquire dark-rate spectrum at each voltage value.

Correction factor α :

$$\alpha \cdot N_{ped}^{dark} = N_{ped}^{dark*} \stackrel{!}{=} N_{tot}^{dark}$$

$$\Rightarrow \alpha = \frac{N_{tot}^{dark}}{N_{ped}^{dark}}$$

$$n_{pe} = -\ln \left(\frac{\alpha \cdot N_{ped}}{N_{tot}} \right) = -\ln \left(\frac{N_{ped}}{N_{tot}} \right) + \ln \left(\frac{N_{ped}^{dark}}{N_{ped}} \right)$$



SiPM Positioning

- All light should hit the active SiPM-Surface.
- $\varnothing=0.6\text{mm}$ aperture was used for measurements with pulsed laserdiodes.
- Plateau on top allows reproducible positioning at maximum.

